

Desy Kolloquium, 5.10.2016

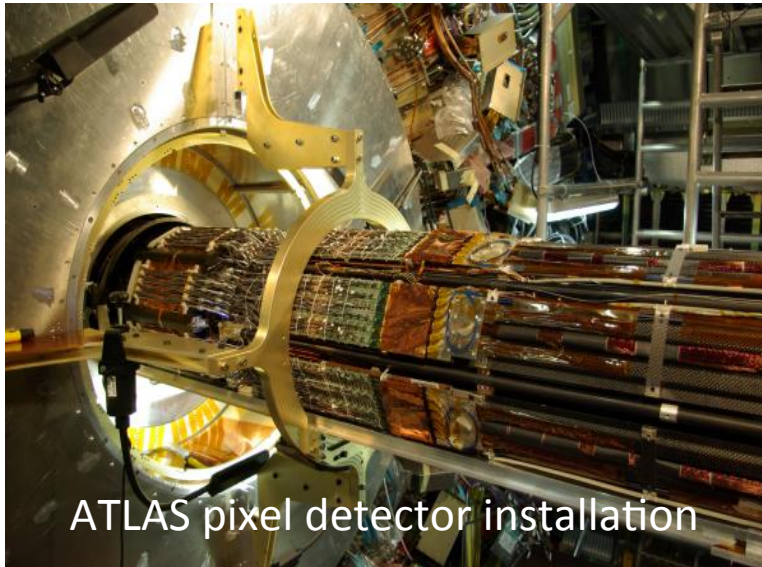
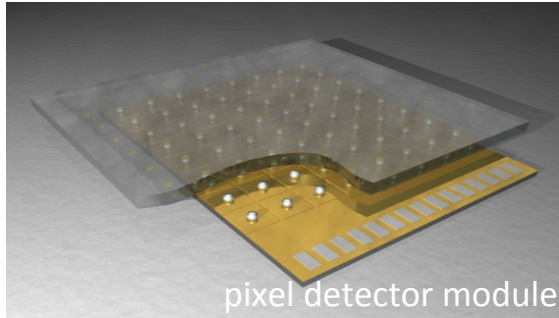
From chips to Higgs and back ... tracking detectors in modern particle physics experiments^(*)

Norbert Wermes
University of Bonn



“From chips to Higgs and back”

detector development



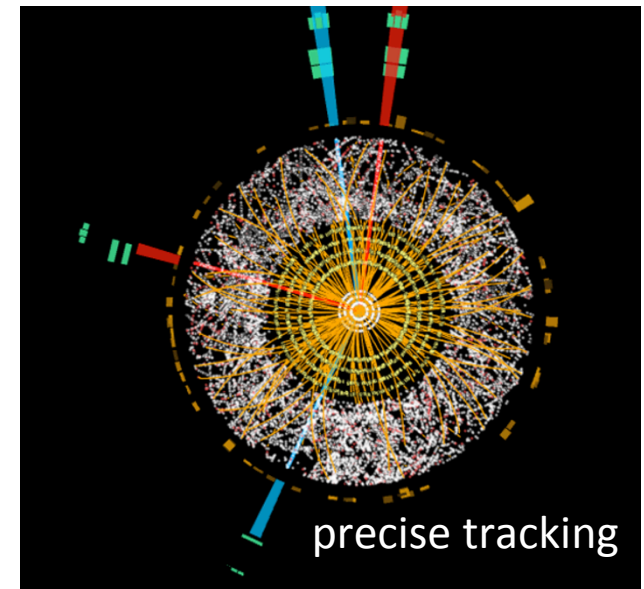
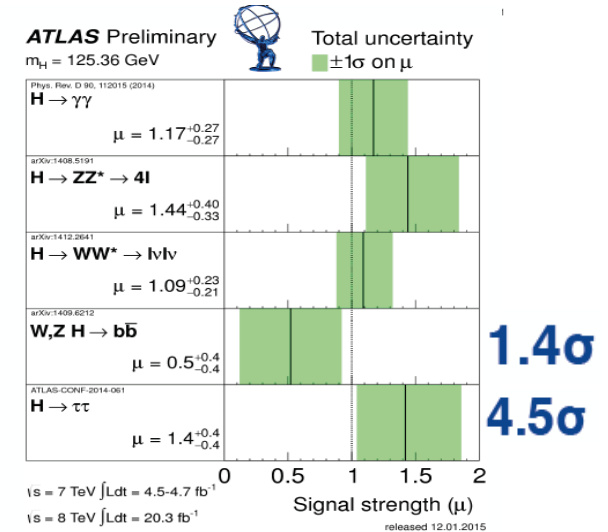
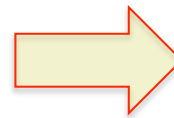
Run 1 (2010-12)

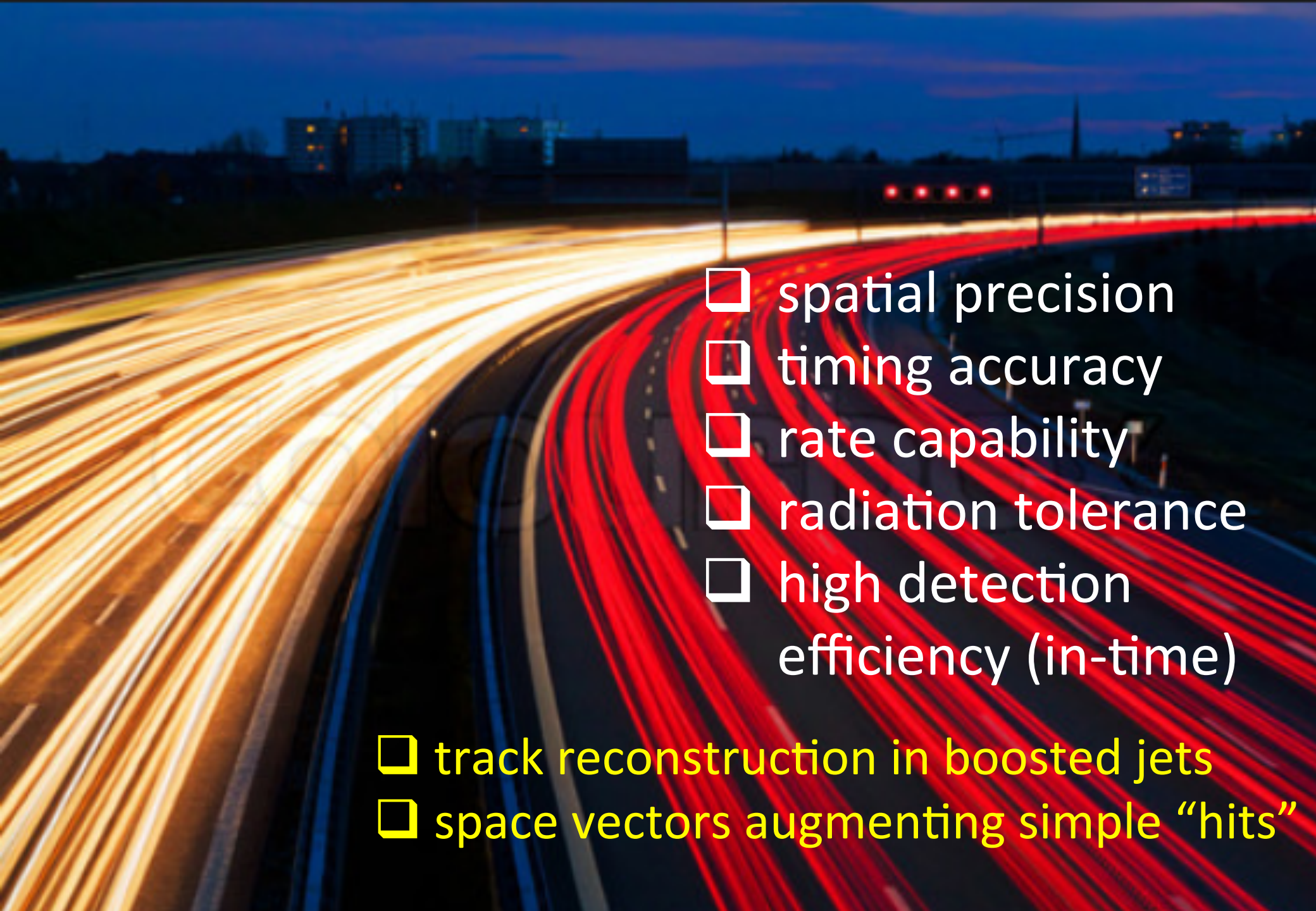
LHC $\cong 10^6 \times$ LEP in track rate !

Run 2 (2015-18): Run 1 $\times 5$

2018 + ... Run 1 $\times 10$?

2026 + ... Run 1 $\times 10 - 20$?

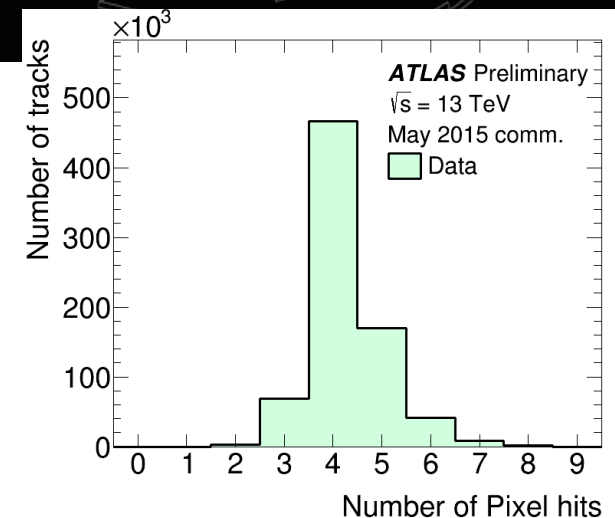
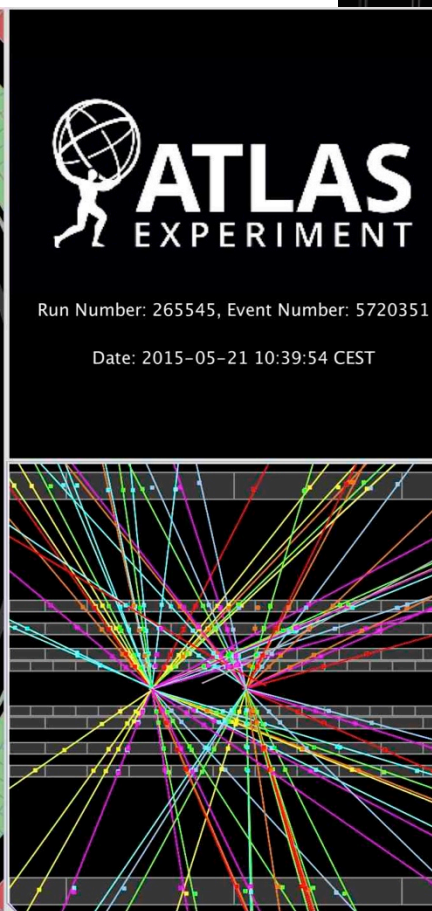
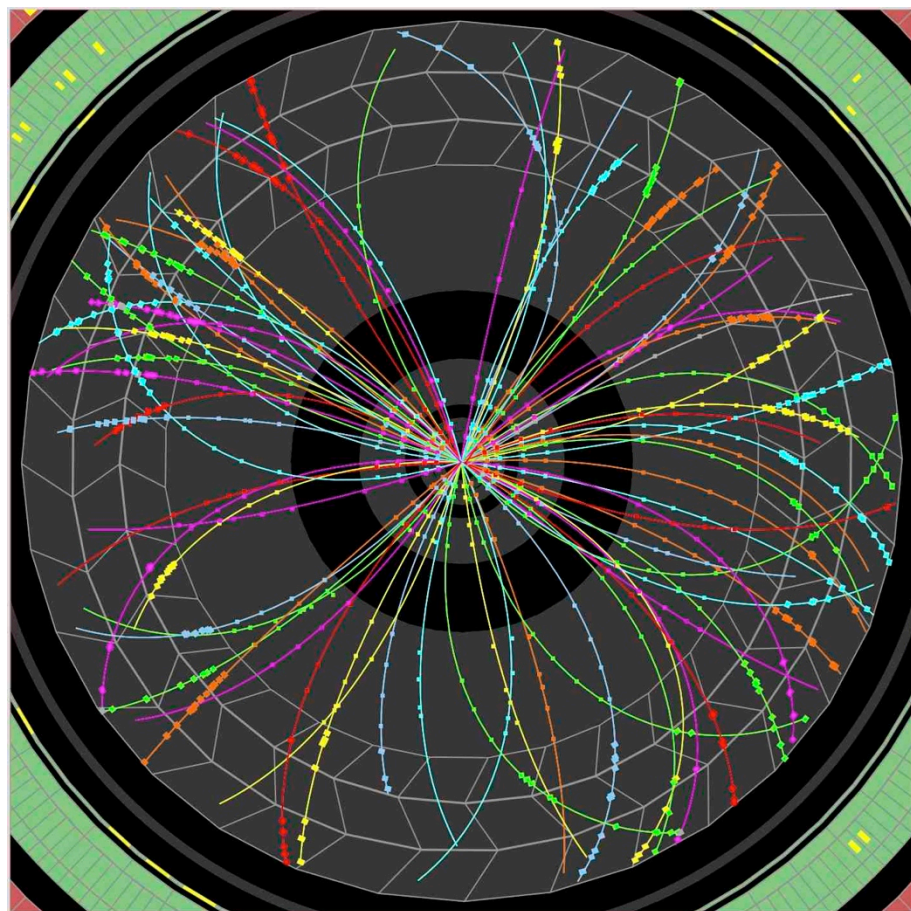
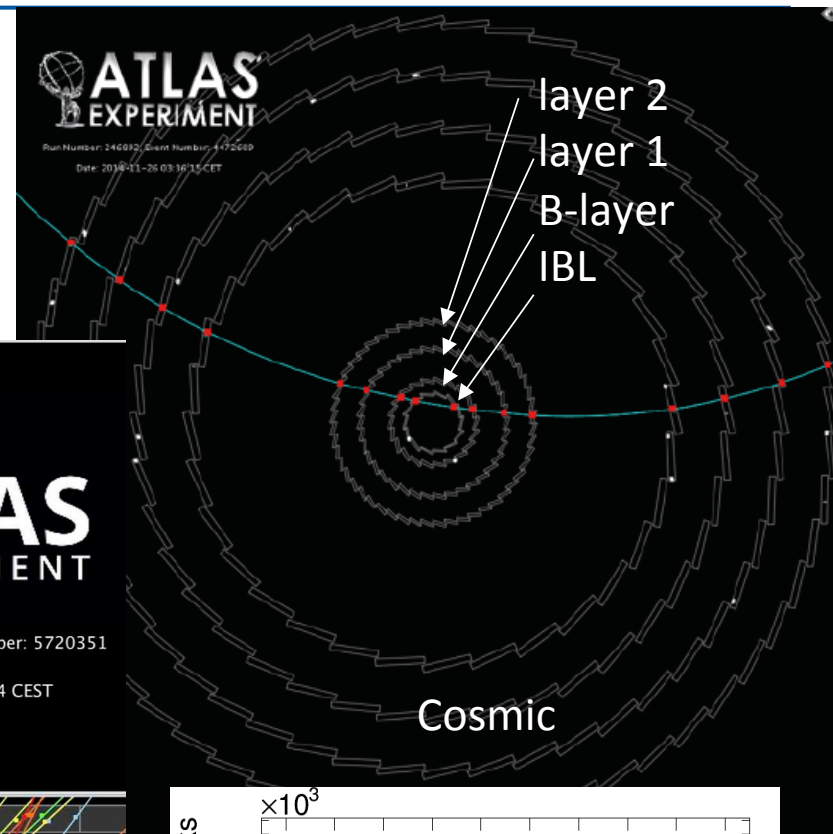


- 
- spatial precision
 - timing accuracy
 - rate capability
 - radiation tolerance
 - high detection efficiency (in-time)

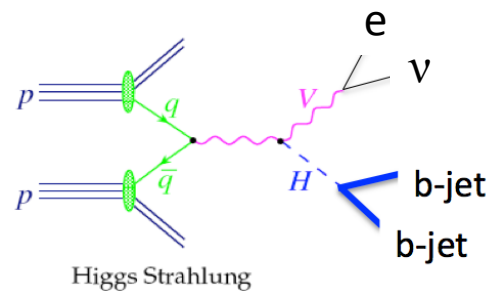
- track reconstruction in boosted jets
- space vectors augmenting simple “hits”

4-hit pixel system!
important for b-quark tagging

low luminosity, 2 interactions

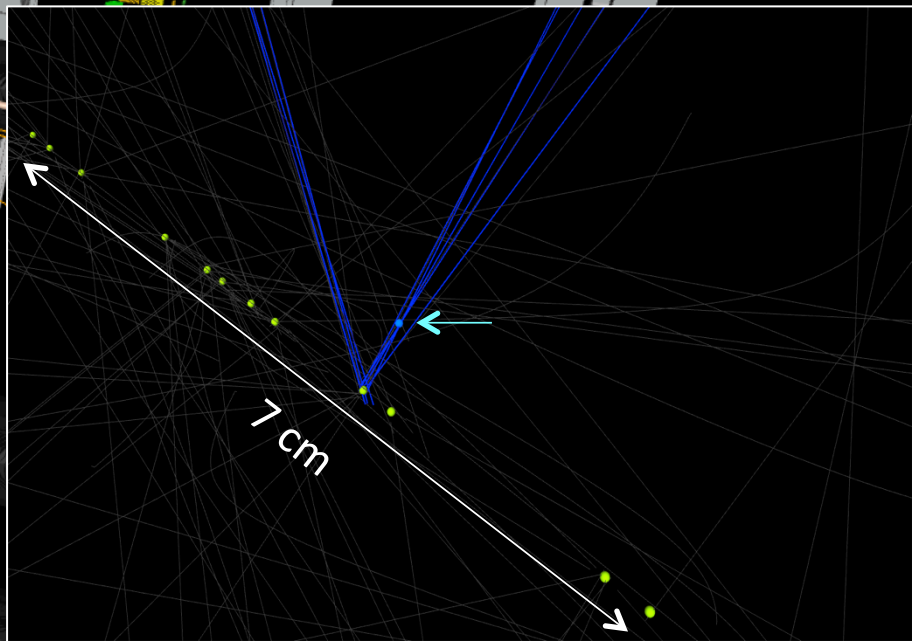
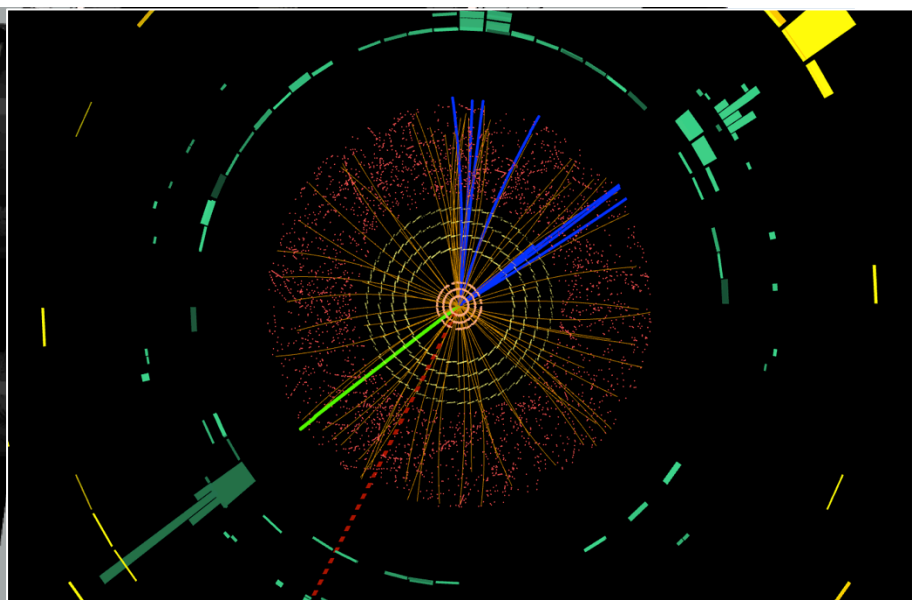
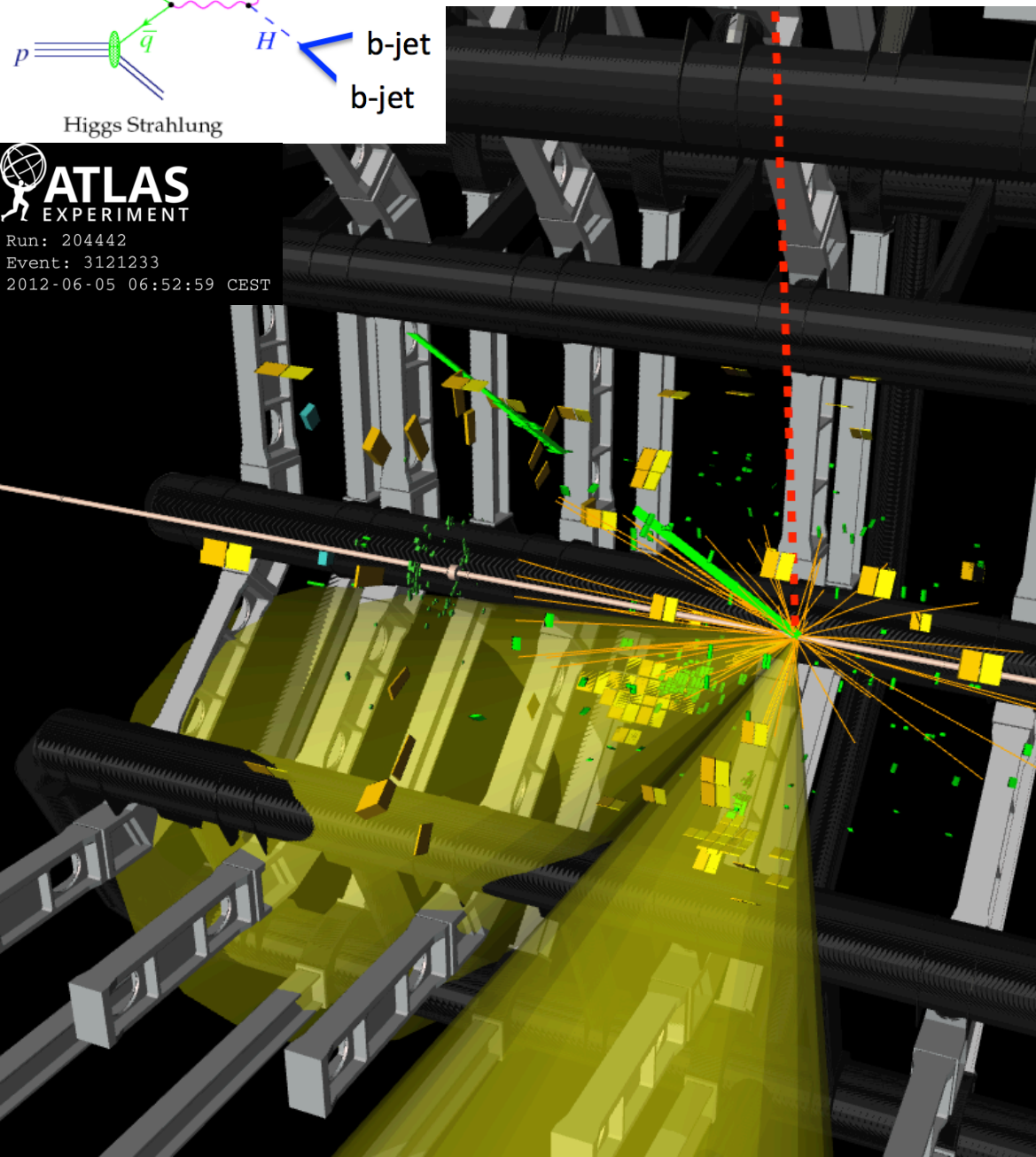


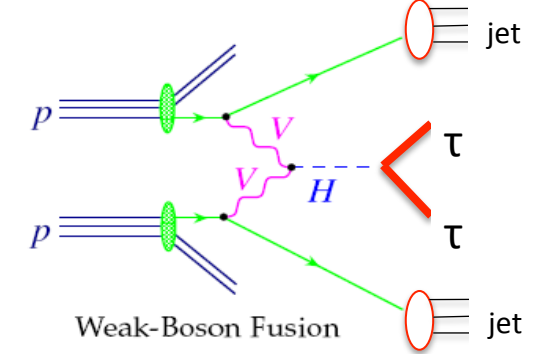
$pp \rightarrow WH \rightarrow \nu l + bb$



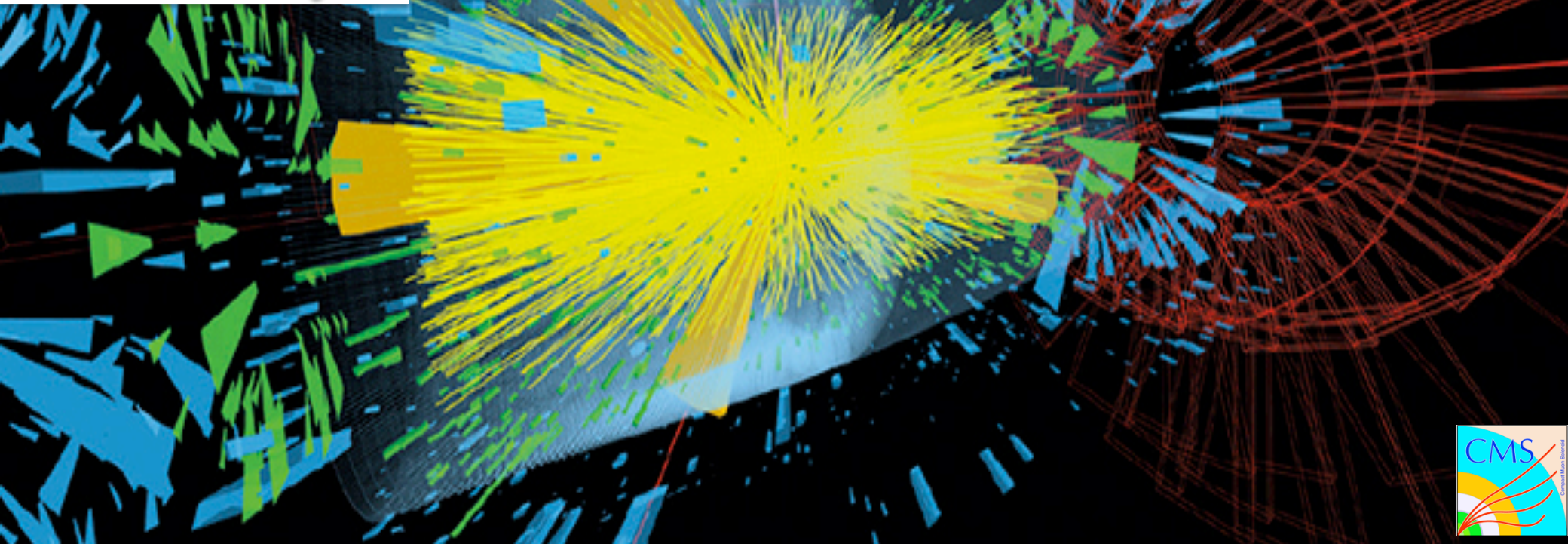
ATLAS
EXPERIMENT

Run: 204442
Event: 3121233
2012-06-05 06:52:59 CEST



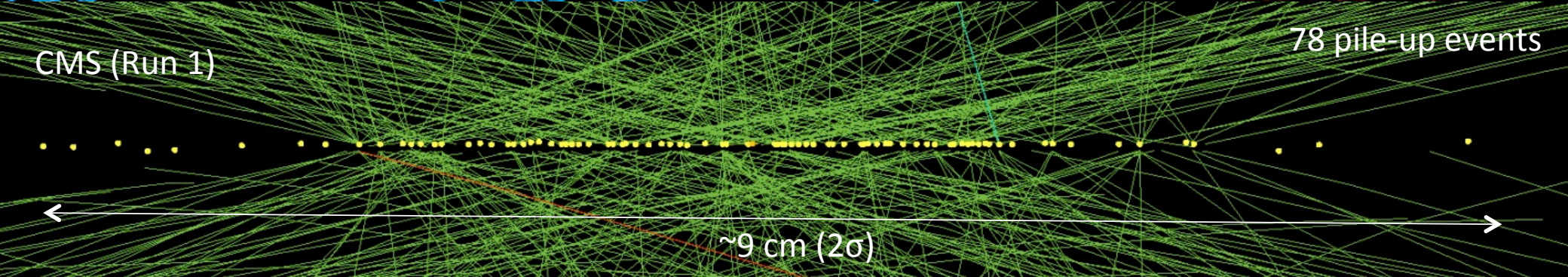


200 pile-up events

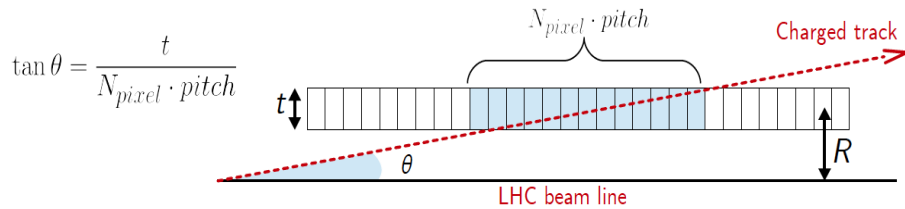


CMS (Run 1)

78 pile-up events



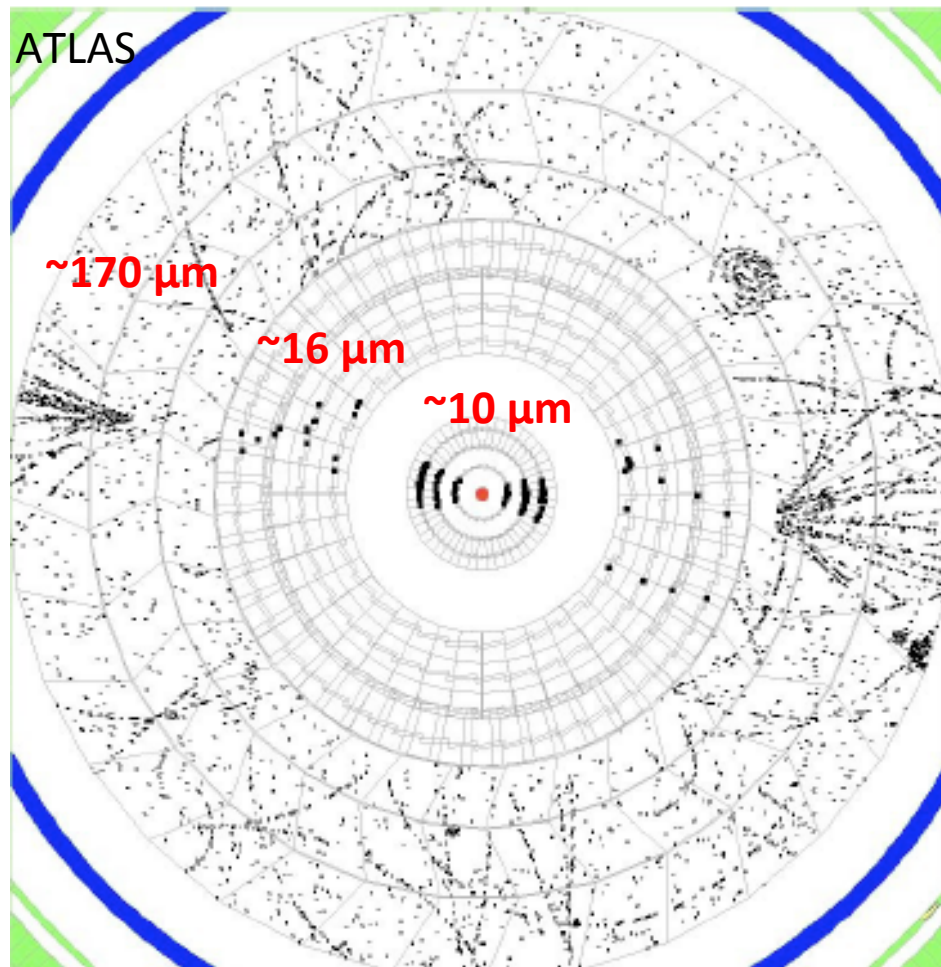
~ 9 cm (2σ)



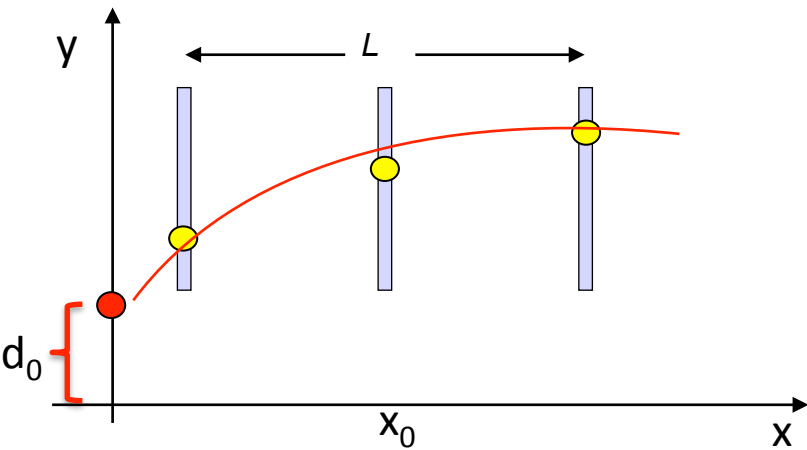
□ provide **precise space points** or space point clusters (**vectors**) originating from ionizing charged particles

- particle **track finding** from patterns of measured hits (at large background & pile-up)
- **momentum** (B-field) and **angle** measurement
- measurement of primary and secondary **vertices**
- multi-**track separation** and vertex-ID in the **core of** (boosted) **jets**
- for low momentum tracks: measurement of the specific ionization (dE/dx)

□ keep the **material** influencing the paths of particles to a **minimum** to avoid scattering in the material and secondary interactions



Good tracking ... p_T and IP measurement as example



approximate helix by a linearized circle
and perform a least square fit

$$\left(\frac{\sigma_{p_T}}{p_T} \right)_{\text{meas}} = \frac{p_T}{0.3|z|} \frac{\sigma_{\text{meas}}}{L^2 B} \sqrt{\frac{720}{N+4}} \otimes \sigma_{MS}$$

$$[p_T] = \text{GeV}/c, [L] = \text{m}, [B] = \text{T} \quad \text{Gluckstern NIM 24 (1963) 381}$$

$$\sigma_{d_0} = \frac{\sigma_{\text{meas}}}{\sqrt{N}} \sqrt{1 + r^2 \frac{12(N-1)}{(N+1)} + r^4 \frac{180(N-1)^3}{(N-2)(N+1)(N+2)} + r^2 \frac{30N^2}{(N-2)(N+2)}} \otimes \sigma_{MS}$$

$r = x_0/L = \text{extrapolation parameter}$

- optimize σ_{meas} until other effects dominate (e.g. MS)
- $1/L^2$: the longer L the better
- place first plane as near as possible to the prod. point
- p_T resol. linearly better with B-field strength ...
but more confusion if many tracks
- Increasing N improves the resolution, but only as $1/\sqrt{N}$

Technology most often used: Si - detectors

PRO – high resolution $\sigma_{\text{meas}} \sim 10 \mu\text{m}$

CON – expensive

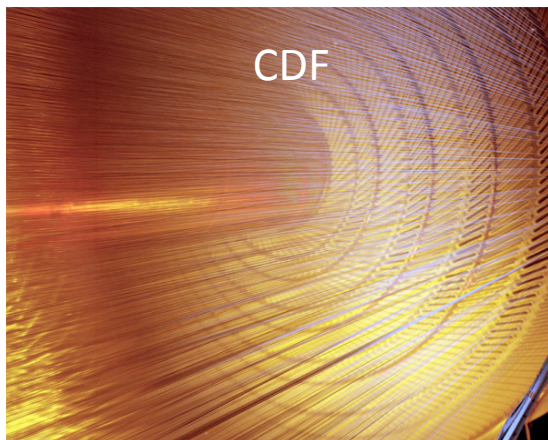
– small N

– small L

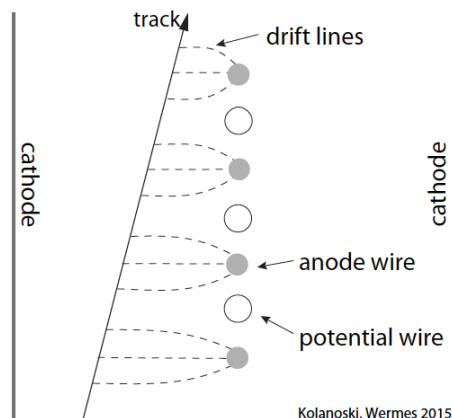
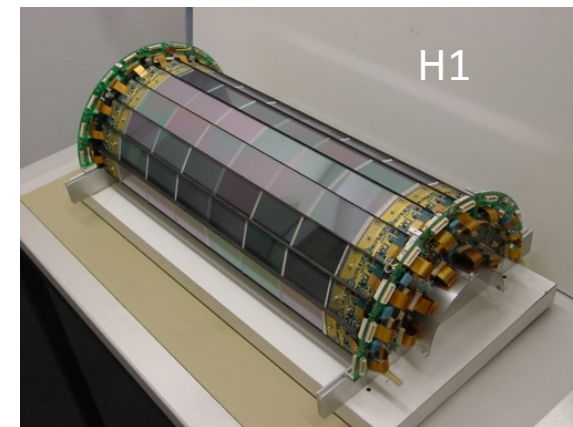
– small $X_0 \Rightarrow$ large mult. scatt.

PRO – high rate capability

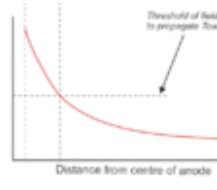
Gas-filled versus semiconductor detectors



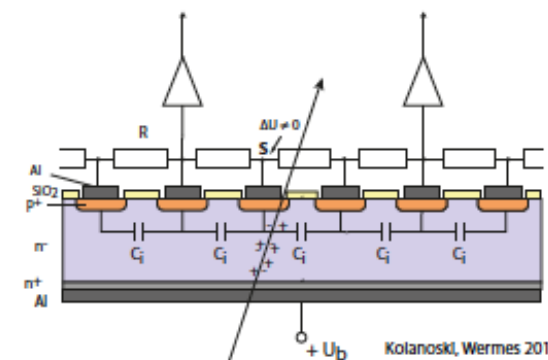
++	material	-
+	N_{meas}	--
low	cost	high
--	rate/speed	++
100 μm	resolution	10 μm



field near wire
 $E(r) \sim 1/r$



$\Rightarrow$ gas amplification

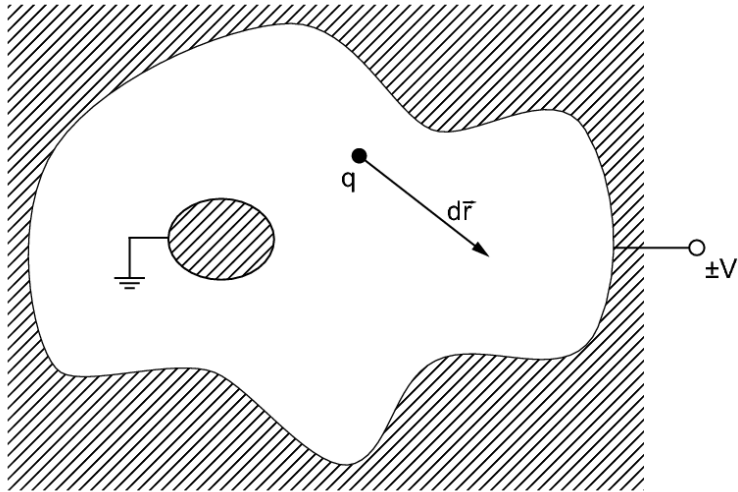


linear E

26 eV needed (Ar) per e/ion pair
94 e/ion pairs per cm
 intrinsic amplification **typ. 10^5**
 typ. noise: > 3000 e- (ENC)

3.65 eV (Si) needed per e/h pair
 $\sim 10^6$ e/h pairs per cm (20 000/250 μm)
 no intrinsic amplification
 typ. noise: 100 e- (pixels) to 1000 e- (strips)

Some basics: How the signal is generated in a detector ...



how does a moving charge couple to an electrode ?

- respect Gauss' law and find

Shockley- Ramo theorem

(Shockley: J Appl.Phys 1938, Ramo: 1939)

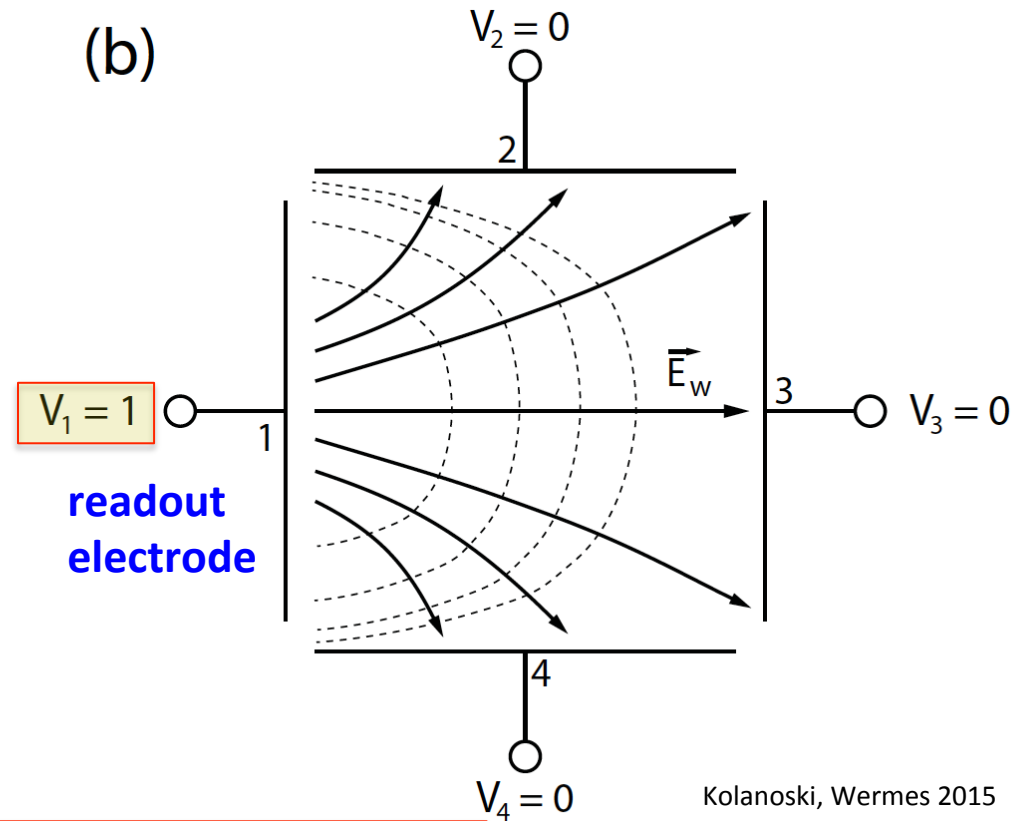
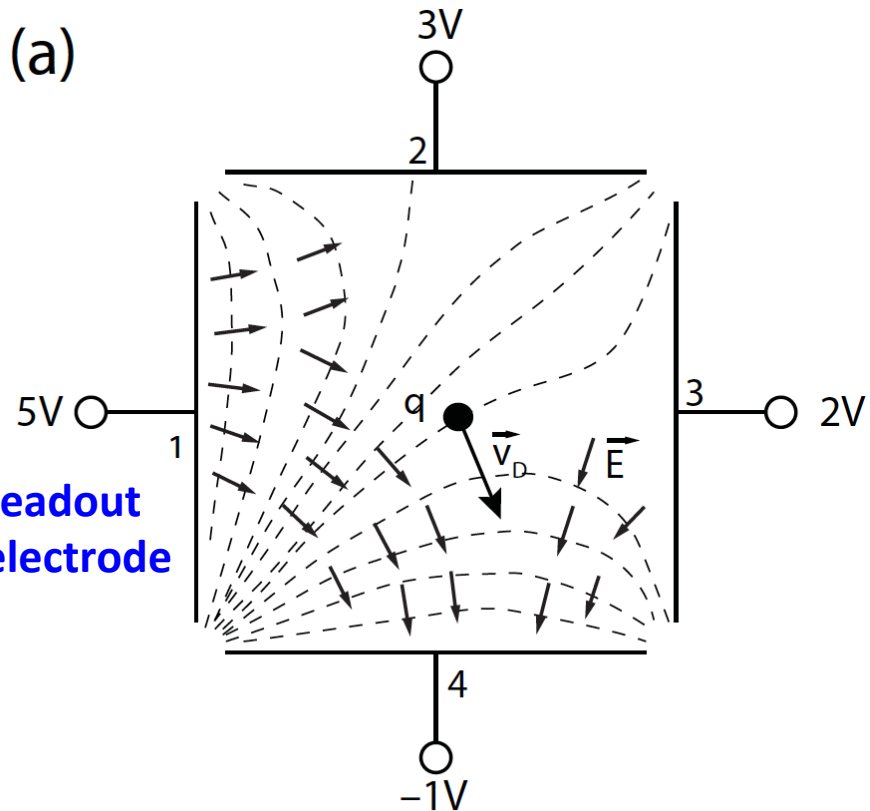
$$dQ = q \vec{\nabla} \phi_w d\vec{r}$$

induction (weighting) potential

$$i_S = -\frac{dQ}{dt} = q \vec{E}_w \vec{v}$$

they determine how charge movement couples to a specific electrode

weighting field

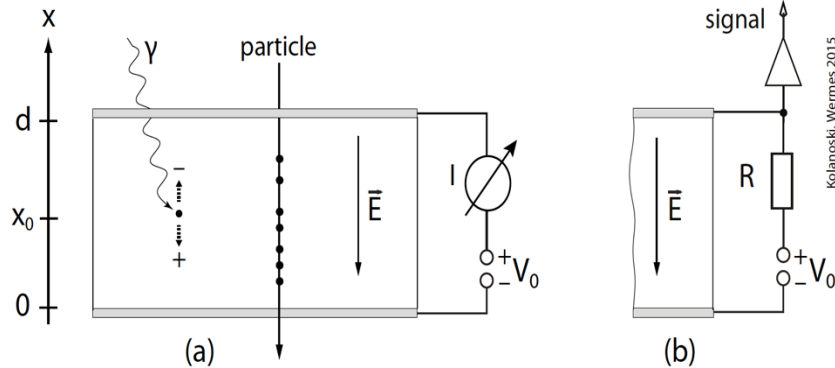


Kolanoski, Wermes 2015

$$i_S = -\frac{dQ}{dt} = q\vec{E}_w\vec{v}$$

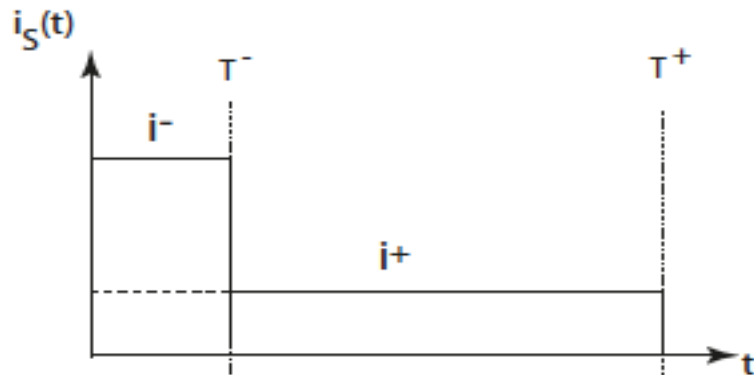
Recipe: To compute the weighting field of a readout electrode i , set voltage of electrode i to 1 and all other electrodes to 0.

parallel plate detector (gas filled)



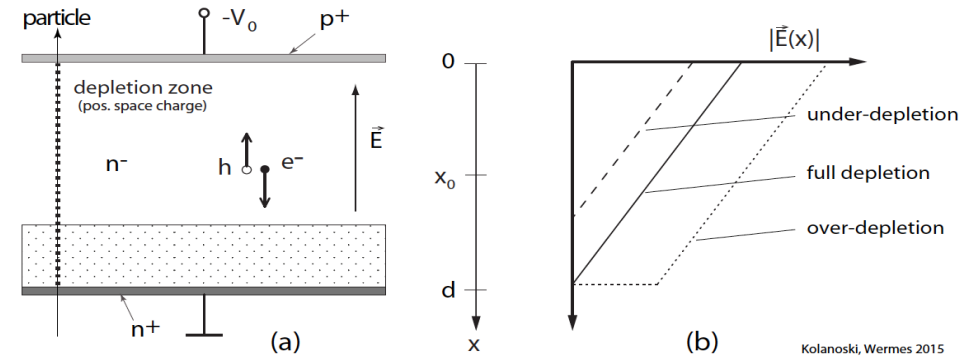
$$\vec{E}_w = -\frac{1}{d}\vec{e}_x$$

velocity ($v=\mu E$) almost const.



$$Q_{tot} = \int_0^{T^+} i(t)dt = Q_s^+ + Q_s^- = \pm e$$

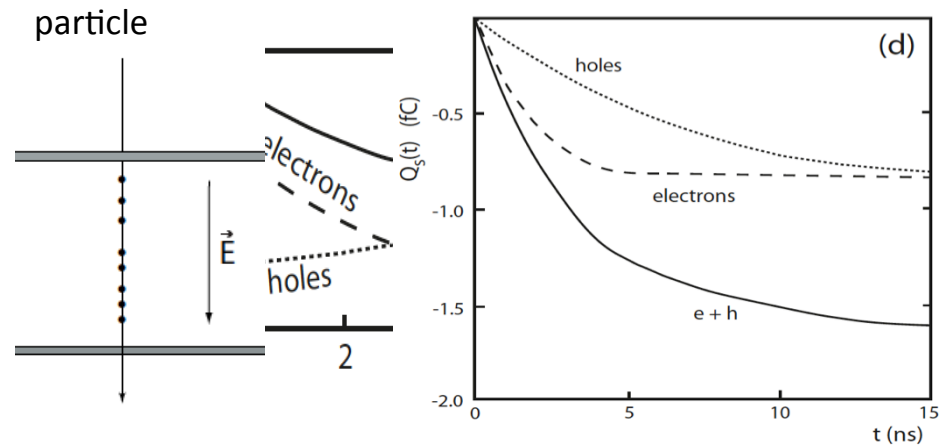
parallel plates with space charge (i.e. Si)



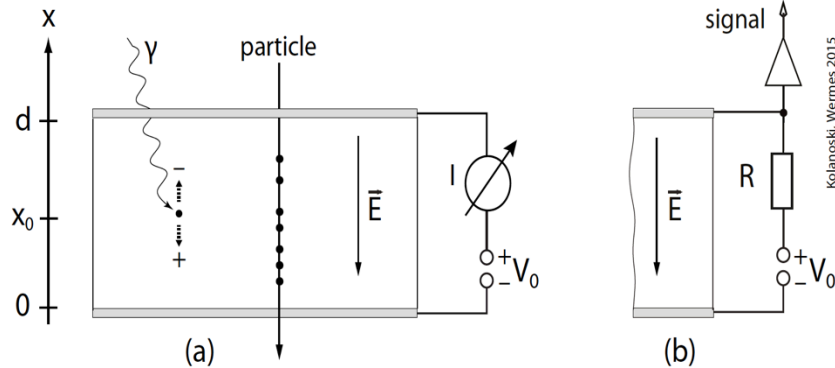
$$\vec{E}_w = -\frac{1}{d}\vec{e}_x$$

$$v_e = \dot{x}_e = -\mu_e E(x) = +\mu_e(a - bx)$$

$$\dot{x}_h = -\mu_h(a - bx)$$

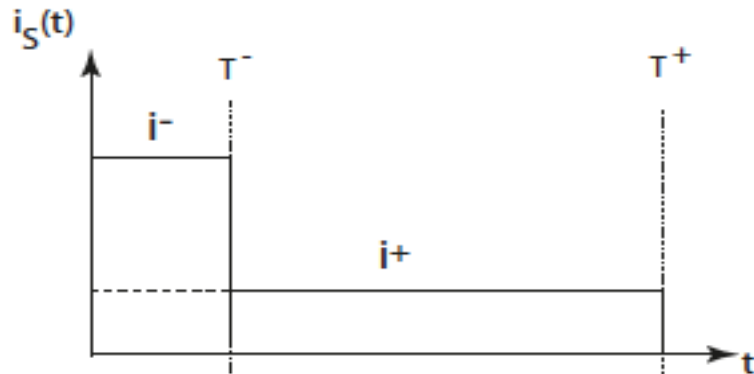


parallel plate detector (gas filled)



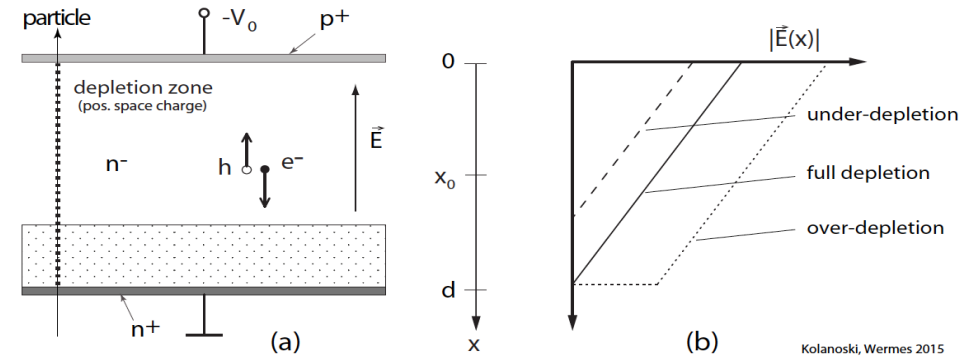
$$\vec{E}_w = -\frac{1}{d}\vec{e}_x$$

velocity ($v=\mu E$) almost const.



$$Q_{tot} = \int_0^{T^+} i(t) dt = Q_s^+ + Q_s^- = \pm e$$

parallel plates with space charge (i.e. Si)

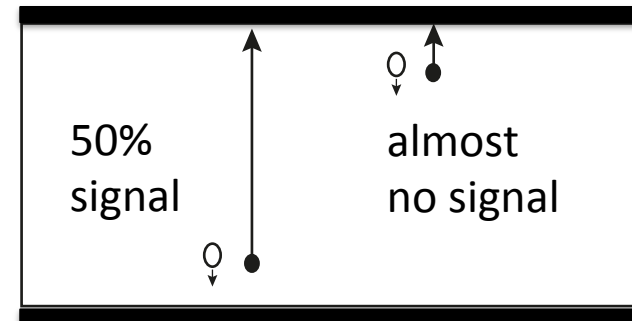


$$\vec{E}_w = -\frac{1}{d}\vec{e}_x$$

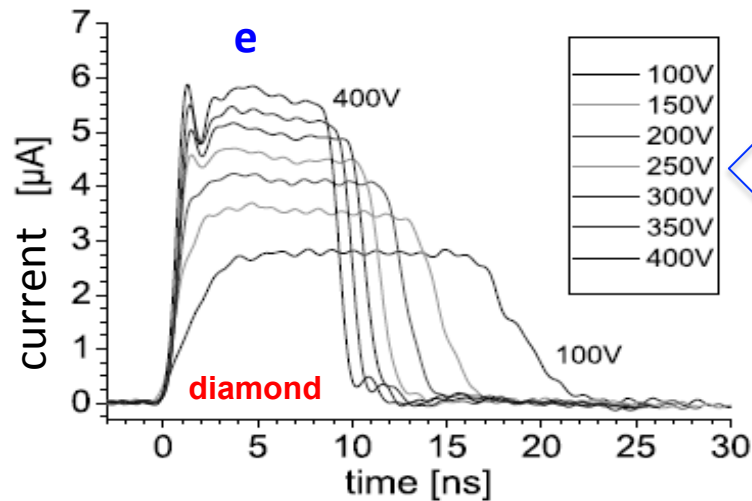
$$v_e = \dot{x}_e = -\mu_e E(x) = +\mu_e(a - bx)$$

$$\dot{x}_h = -\mu_h(a - bx)$$

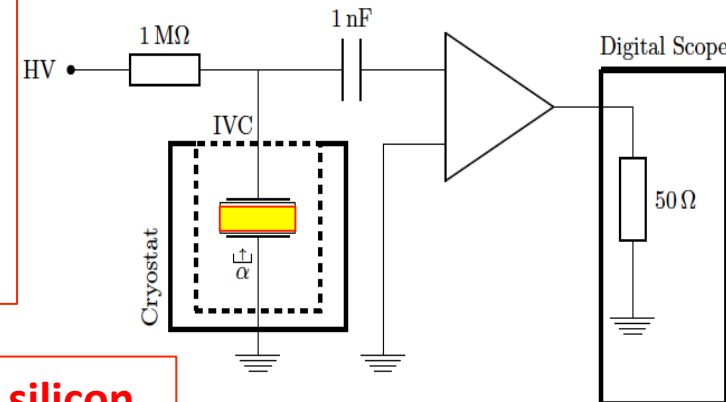
dangerous e.g. in CdTe



Current pulse measurements: TCT technique



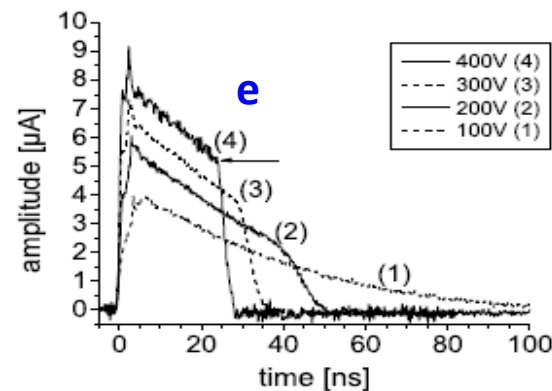
single crystal **diamond** is like a parallel plate detector filled with a dielectric w/o space charge



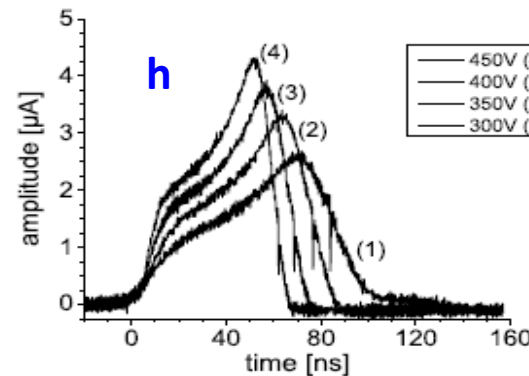
1mm pn – Diode **silicon**

- same weighting field
- different electric field

Fink, Lodomez, Kruger, Pernegger, Weilhammer, NW, NIM A 565 (2006), 227

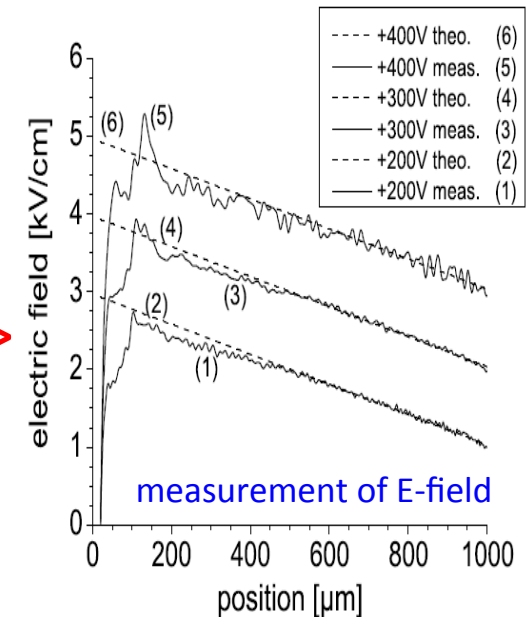


(a) Electron signals from α -particles impinging on the cathode.



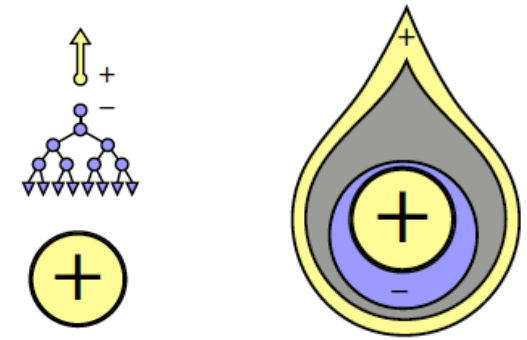
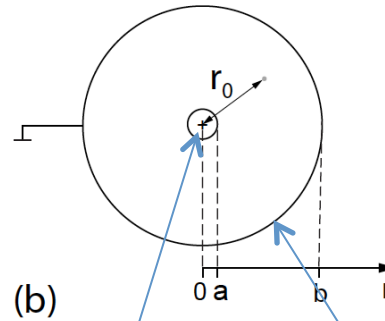
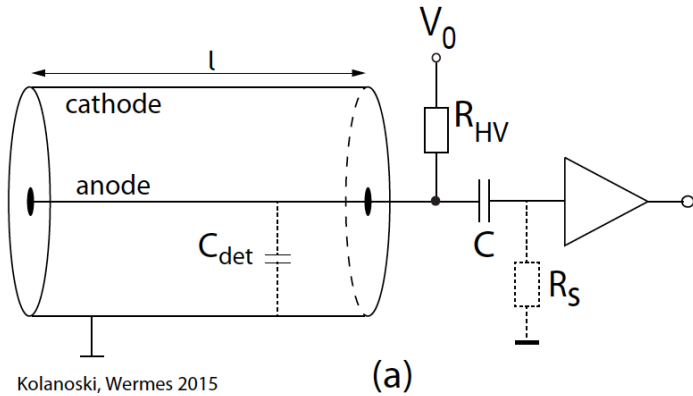
(b) Hole signals from α -particles impinging on the anode.

=>



measurement of E-field

Signal development in a wire configuration



- $E(r) \sim 1/r \Rightarrow$ gas amplification $\Rightarrow$ “signal” current starts only close to the wire
- Shockley-Ramo-recipe: $\phi_w(a) = 1, \phi_w(b) = 0$ (*)

$$\vec{E}_W(r) = \frac{1}{r} \frac{1}{\ln \frac{b}{a}} \vec{e}_r$$

$$\phi_W(r) = -\frac{\ln r/b}{\ln \frac{b}{a}}$$

which fulfills (*)

$$\left(\frac{Q_S^-}{Q_S^+} \right)_{r_0=b/2} \approx 9$$

far away from wire
($a=10 \mu\text{m}$, $b=10 \text{ mm}$)

$$Q_S^{\text{tot}} = Q_S^- + Q_S^+ = -Ne \Rightarrow \left(\frac{Q_S^-}{Q_S^+} \right)_{r_0} = \frac{\ln r_0/a}{\ln b/r_0}$$

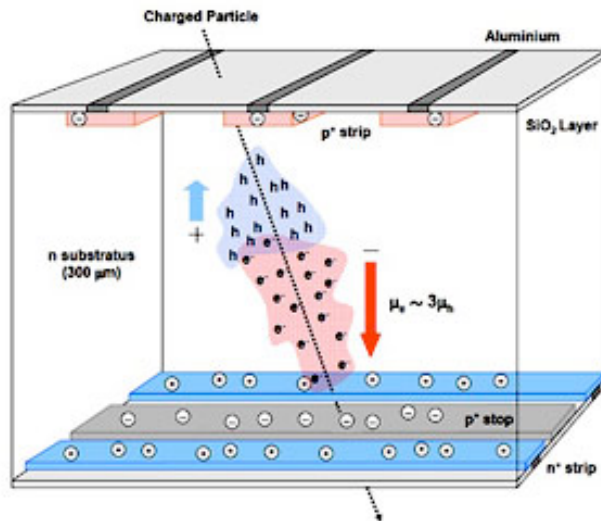
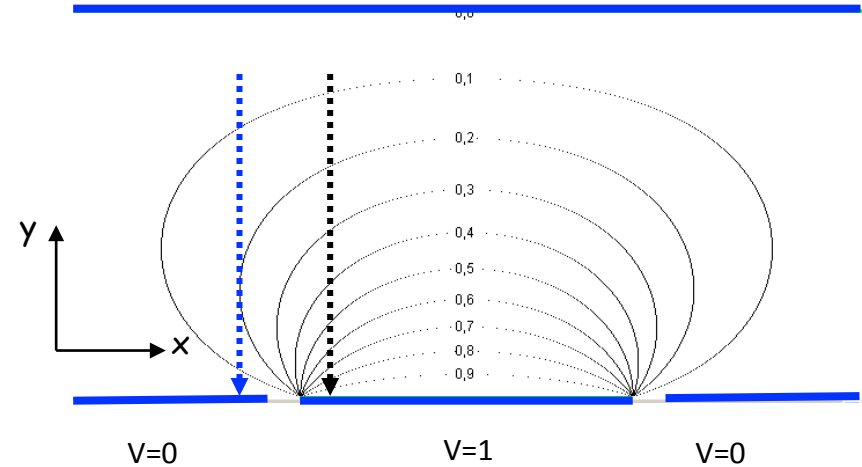
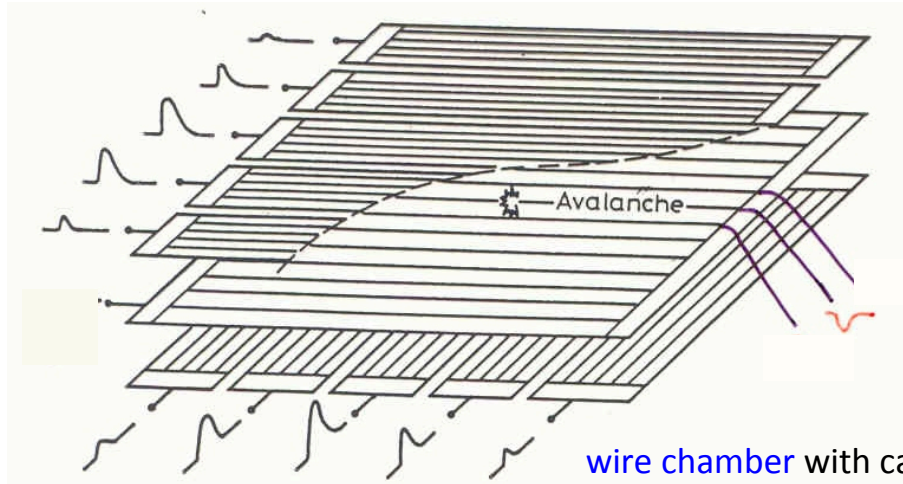
$$\left(\frac{Q_S^-}{Q_S^+} \right)_{r_0=a+\epsilon} \approx 0.01 - 0.02$$

near wire

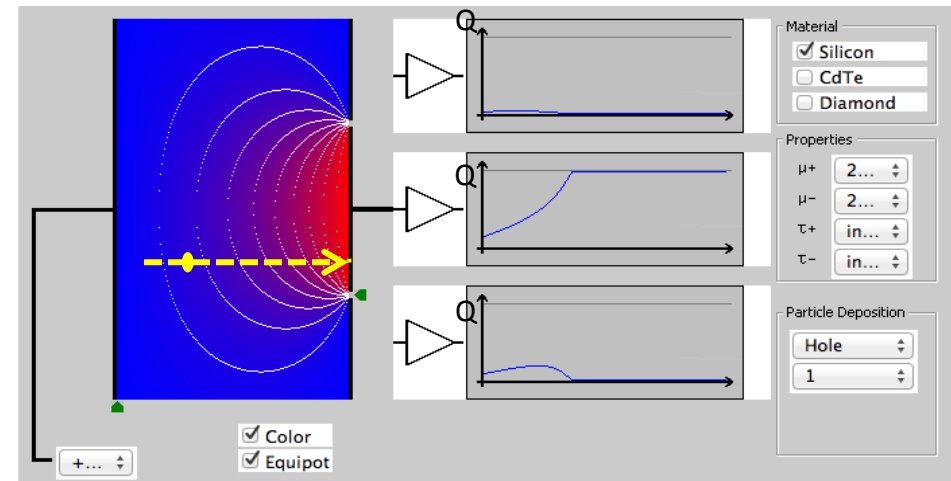
wire chamber signals are governed by away moving ions

Structured electrodes

signals are induced on **BOTH (ALL)** electrodes => exploit for second coordinate readout



double sided silicon strip detector



□ particle rates ($\mathcal{L} = 10^{34} \text{ cm}^{-2} \text{ s}^{-1}$)

note: heavy ions: $\mathcal{L} = 10^{27} \text{ cm}^{-2} \text{ s}^{-1}$

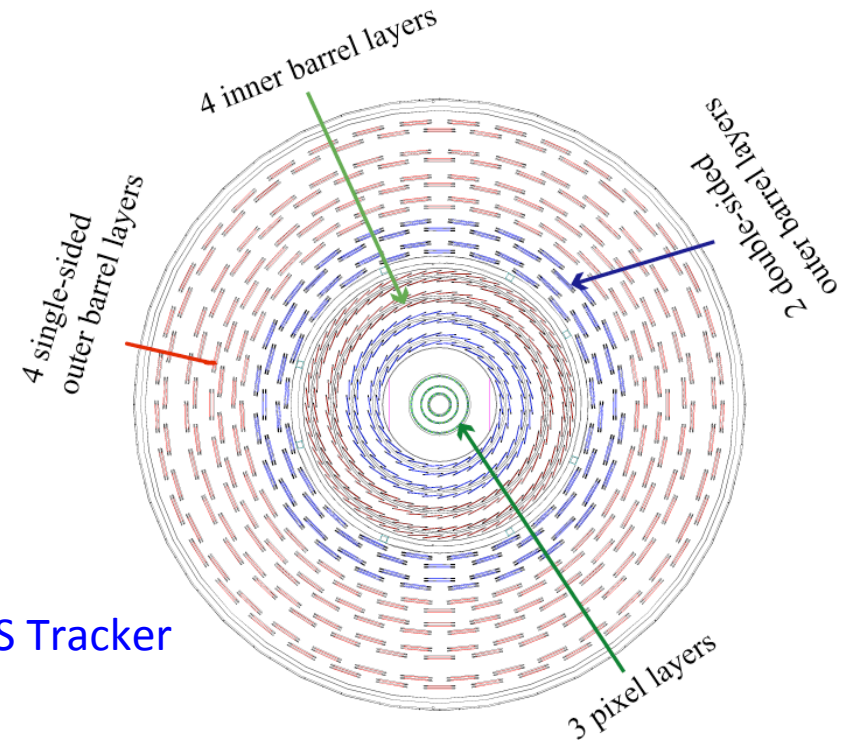
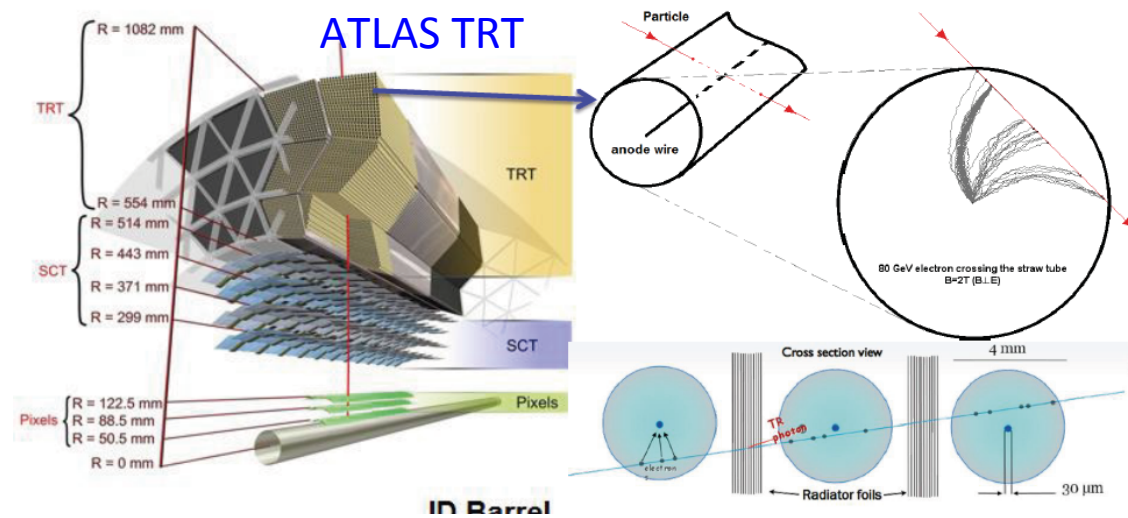
- bunch crossing every 25 ns
- $N_{\text{trk}} = \sigma \mathcal{L} = 100 \text{ mb} \times 10^{34} \text{ cm}^{-2} \text{ s}^{-1} \times 120 \approx 10^{11} \text{ tracks/s}$ in $4\pi = 10^6 \times \text{LEP}$
- @ $r = 5 \text{ cm} \Rightarrow 9.5 \text{ tracks/cm}^2/25 \text{ ns}$, but only $10^{-4} \text{ per pixel}$ ($100 \times 100 \text{ } \mu\text{m}^2$)

□ radiation level (@ $r = 5 \text{ cm}$, per detector lifetime)

- total ionizing dose (TID) = energy/mass (J/kg) = 100 Mrad $\rightarrow$ 1 Grad
- non ionizing fluence (NIEL, breaks the lattice) = $10^{15} \text{ particles per cm}^2$ $\rightarrow 10^{16} \text{ cm}^{-2}$
- effects: ageing on wires, lattice damage, glue brittle, electronics, ...

way out

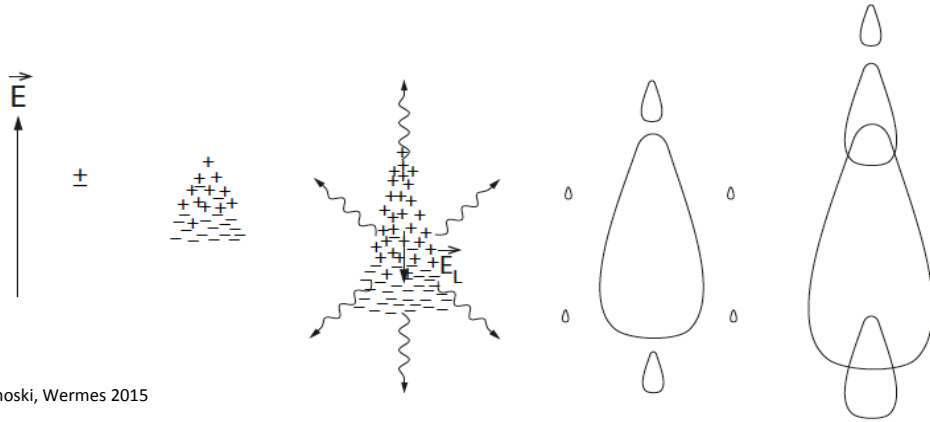
- gas-filled detectors with **small cells**
- timing precision $\ll 25$ ns
- **solid state detectors**
 - micro structuring
=> finest granularity
 - **but:** sensitive to radiation



CMS Tracker

Example for “timing”: RPCs (resistive plate chambers)

- target: **high timing precision** (trigger and timing chambers, e.g. ATLAS Muon Spectrometer)



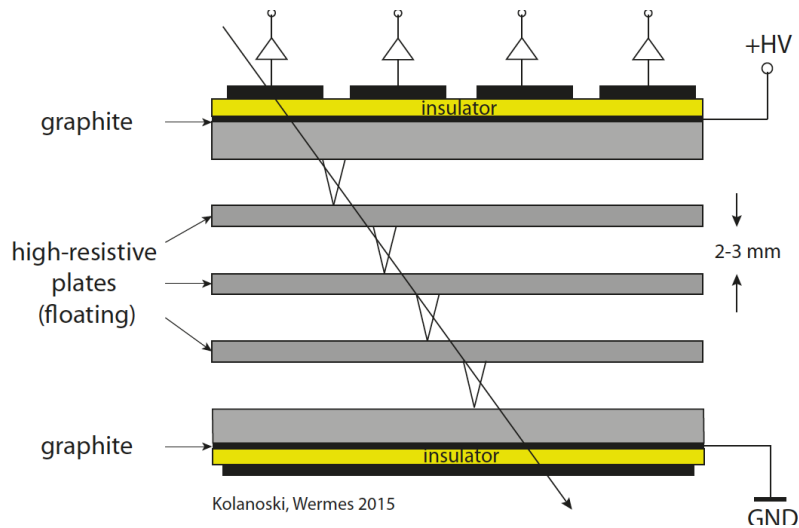
- gas filled chambers w/ large signals
 - operated in **avalanche** mode (≥ 10 kV/cm) or in **streamer** mode (~ 100 kV/cm)

- gas with **high ionisation density** and **high quenching efficiency**

e.g. 94.7% $\text{C}_2\text{H}_2\text{F}_4$ + 5% iC_4H_{10} + 0.3% SF_6

“avalanche” $\leftrightarrow$ “streamer”

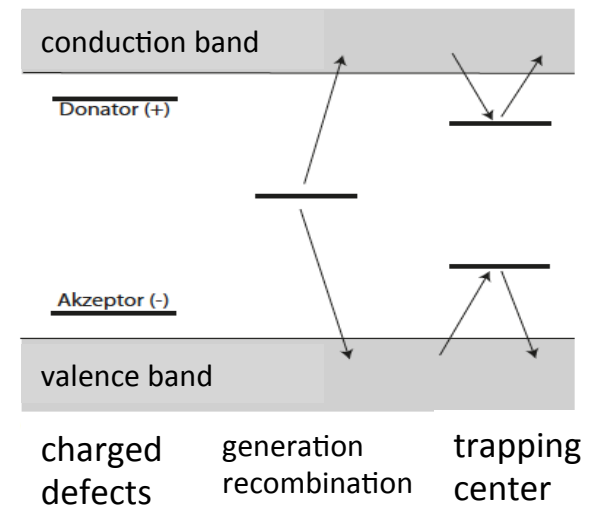
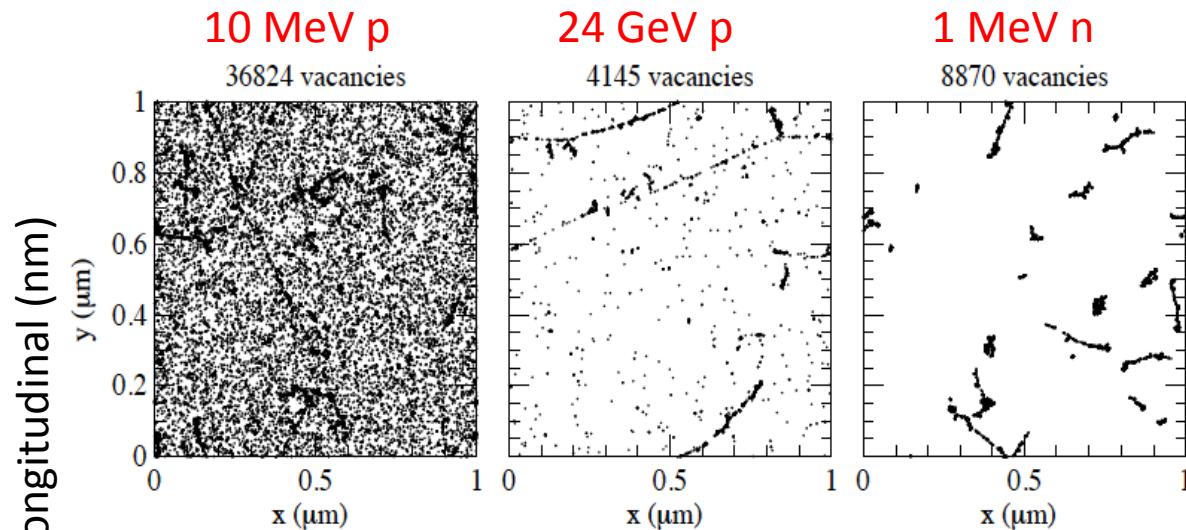
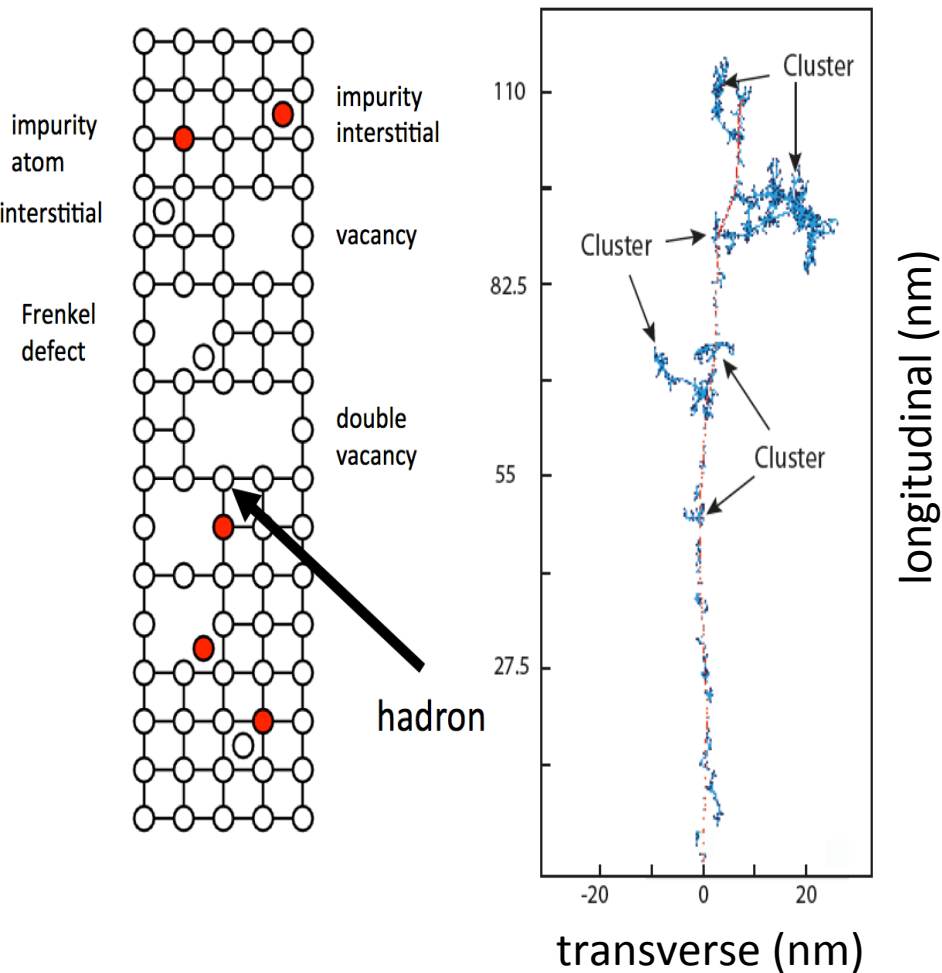
v_{drift} $\leftrightarrow$ photon emission
 10^5 m/s $\leftrightarrow$ 10^6 m/s



	Trigger RPC	Timing RPC
el. Feld	20-50 kV/cm	~ 100 kV/cm
op. mode	avalanche	streamer
signal	< 10 pC	< 100 pC
quench times	shorter	longer
σ_t	1 ns	50 ps
efficiency	98%	75%

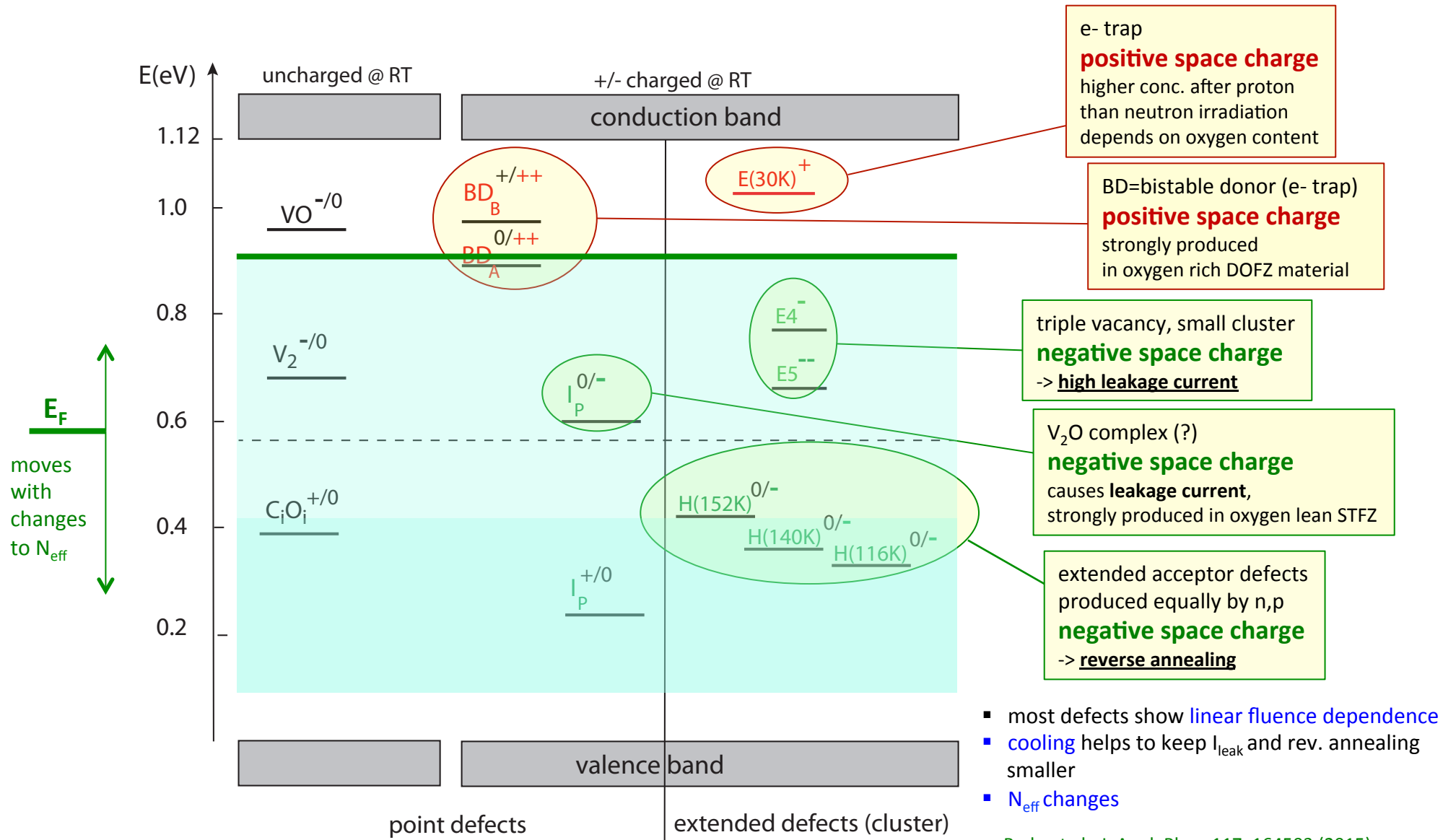
Kolanoski, Wermes 2015

... special at the LHC is the **radiation environment**



threshold energy to **remove an atom**:
Si: 25 eV, **diamond**: 43 eV

Much progress in understanding radiated Si-sensors

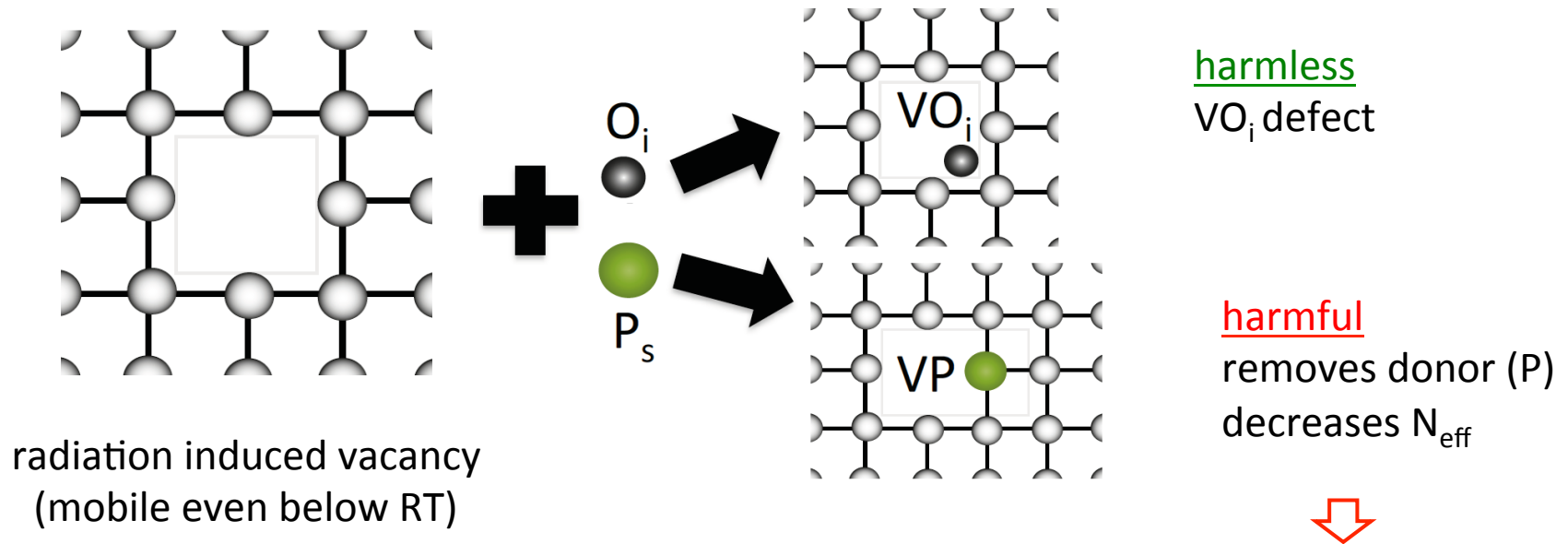


- most defects show **linear fluence dependence**
- **cooling** helps to keep I_{leak} and rev. annealing smaller
- **N_{eff} changes**

Radu et al., J. Appl. Phys. 117, 164503 (2015)
RD50, M. Moll et al., PoS (Vertex 2013) (2013) 026

... and cures (defect engineering ... examples)

- low temperature (-10 °C) operation
- oxygenated silicon
- start with n-implant (e^- collection) in p-substrate material (not available ~1998)

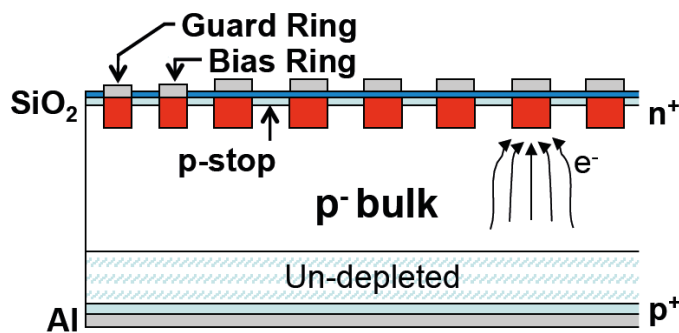
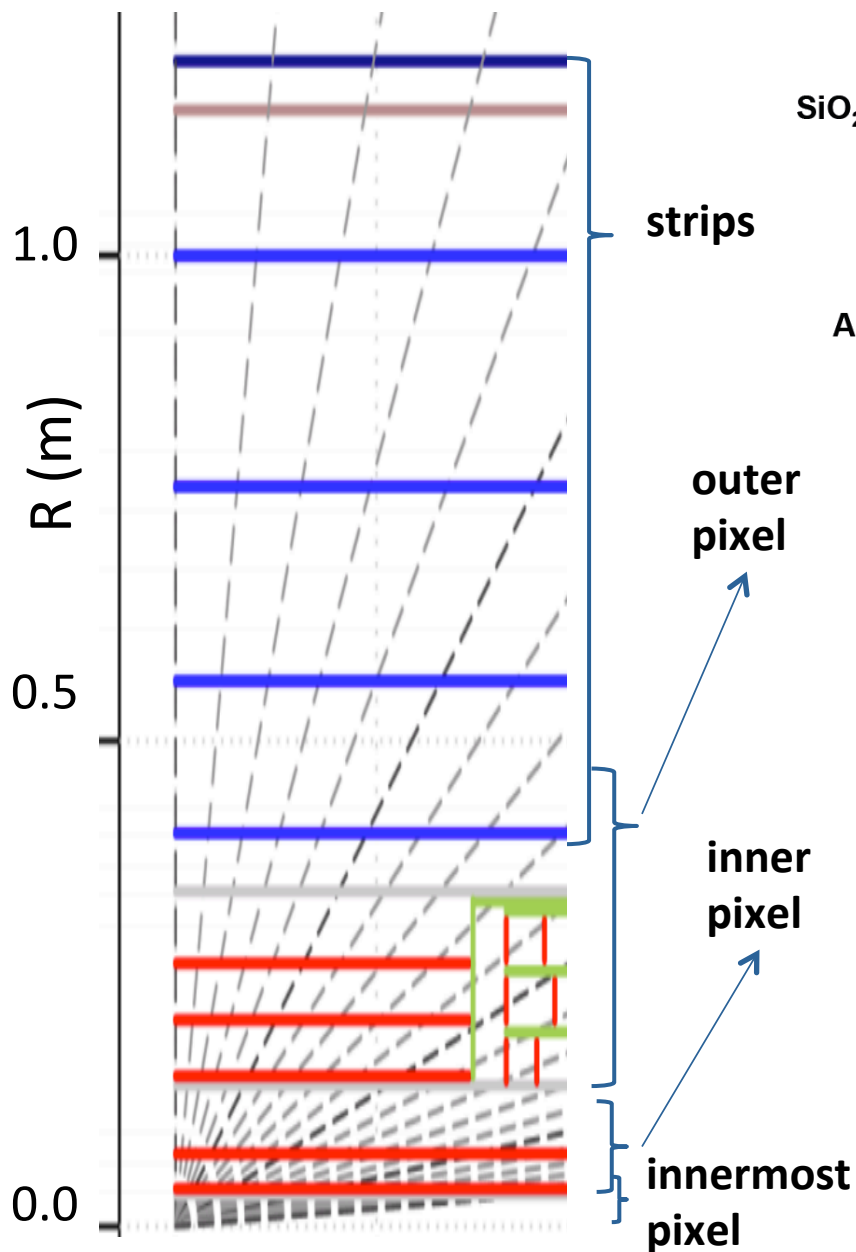


$$[O] \gg [P]$$

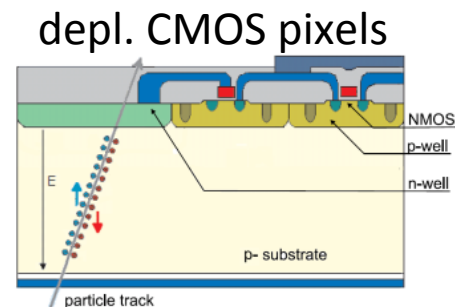
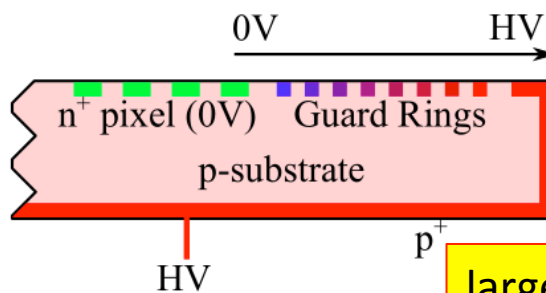
A. Junkes, PoS Vertex 2011 (2011) 035
I. Pintilie et al., Nucl.Instrum.Meth. A611 (2009) 52-68

- for: chip electronics (TID) use thin oxides and special designs

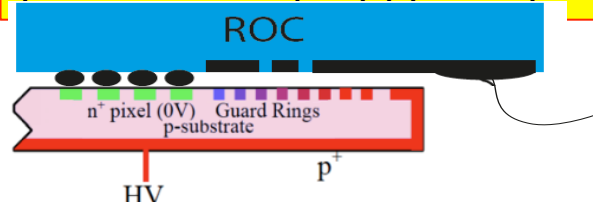
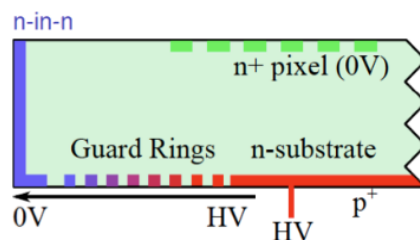
Typical tracker arrangements for the HL-LHC Upgrade ... universität bonn



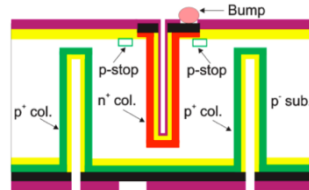
n^+ in p strip modules



large modules
planar n^+ in n (or p) pixels / CMOS?



3D silicon



■ oxide ■ metal ■ passivation
■ p⁺ Si ■ p⁺ poly-Si ■ n⁺ poly-Si ■ p⁺ Si

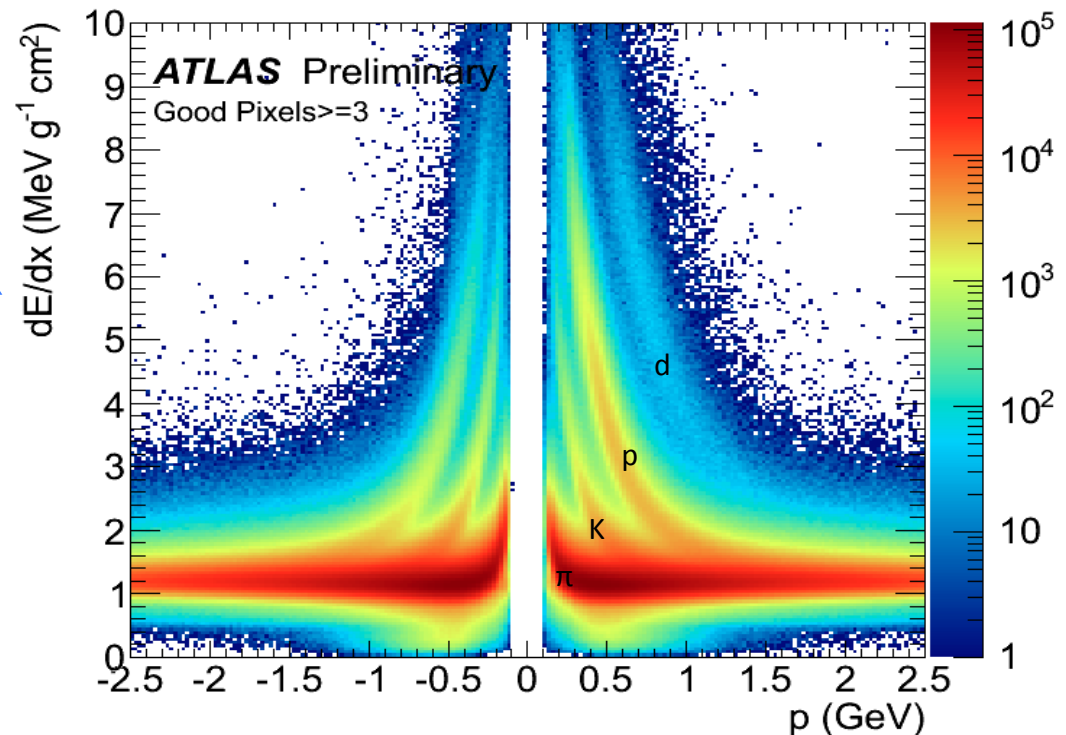
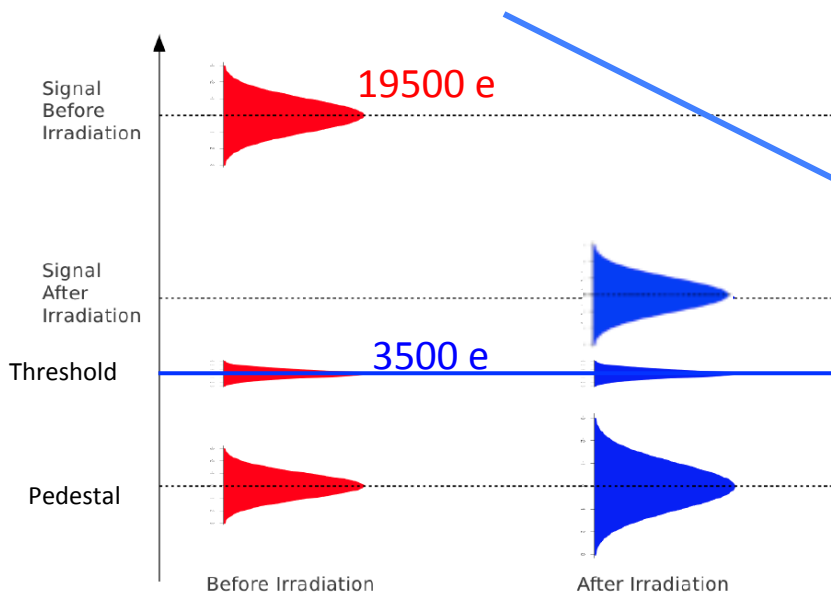
dedicated
rad.-hard
detectors

The typical S/N situation (... here ATLAS)

Signal of a mip in 250 μ m Si $\hat{=}$ 19500 e $^-$ $\rightarrow$ <10000 e $^-$ after irradiation

Charge on more than 1 pixel $\Rightarrow$ S/N > 30 $\rightarrow$ S/N $\sim$ 10

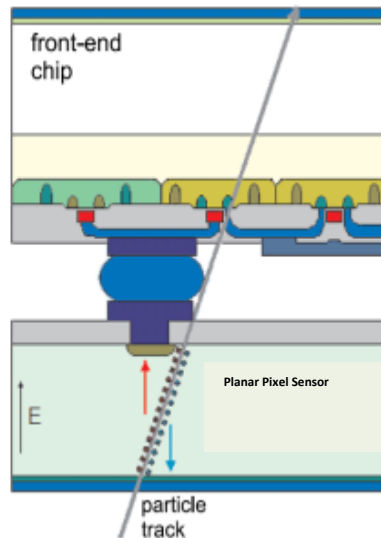
- ☐ Discriminator thresholds = 3500 e, $\sim$ 40 e spread, $\sim$ 170 e noise
- ☐ 99.8% data taking efficiency
- ☐ 95.9% of detector operational
- ☐ ca. 10 μ m x 100 μ m resolution (track angle dependent)
- ☐ 12% dE/dx resolution



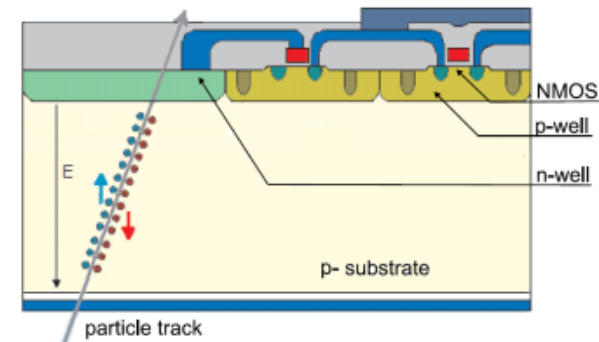
New Developments (Pixels) ... for LHC and others

Is there life after “hybrid pixels”? ... **monolithic**?

Hybrid Pixels

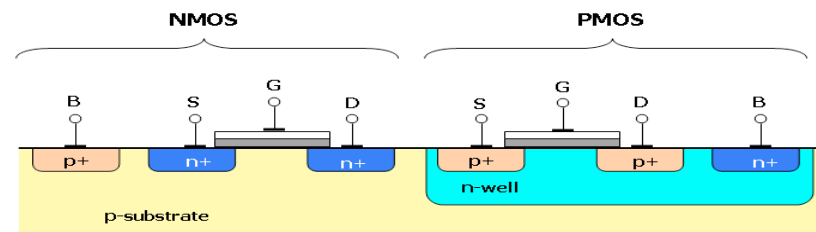


Depleted (fully) Monolithic Active Pixel Sensors (DMAPS)



(commercial CMOS Technology)

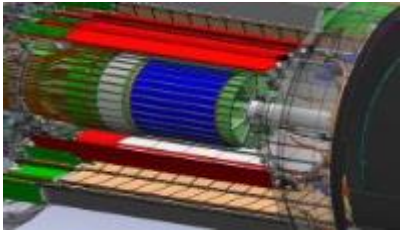
Peric et al., NIM A582 (2007) 876-885 & NIM A765 (2014) 172-176
Mattiazzo, Snoeys et al., NIM A718 (2013) 288-291
Havranek, Hemperek, Krüger, NW et al. JINST 10 (2015) 02, P02013



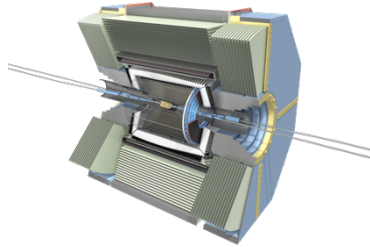
CMOS

Rate and Radiation Levels

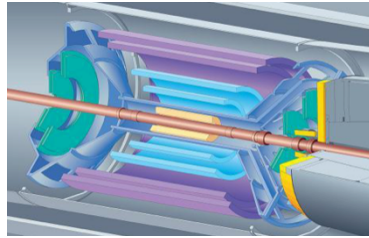
STAR



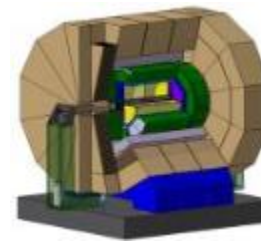
Belle II



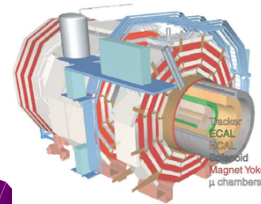
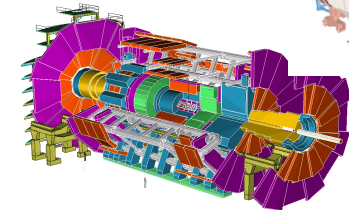
ALICE-(HL)-LHC



ILC



ATLAS



CMS

Numbers for innermost layers ($r \approx 5\text{cm}$,) $\rightarrow$ scale by 1/10 for typical strip layers ($r > 25\text{ cm}$)

	STAR	Belle II	ALICE-LHC heavy ion	ILC	LHC pp	HL-LHC-pp	
						Outer	Inner
BX-time (ns)	110	2	20 000	350	25	25	25
Particle Rate (kHz/mm ²)	4	400	10	250	1 000	1 000	10 000
Φ (n_{eq} /cm ²)	few 10^{12}	3×10^{12}	$> 10^{13}$	10^{12}	2×10^{15}	10^{15}	2×10^{16}
TID (Mrad)*	0.2	20	0.7	0.4	80	50	> 1000

*per (assumed) lifetime
LHC, HL-LHC: 7 years
ILC: 10 years
others: 5 years

in need for

- much less material
- higher resolution
- thinner strips & monolithic pixels

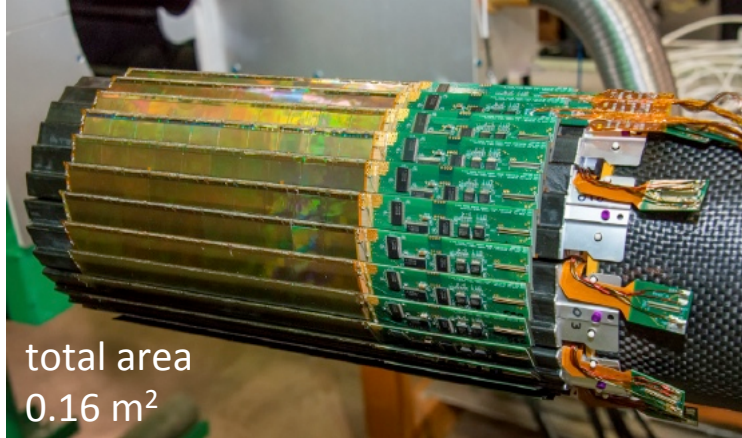
state of the art

- large area strips
- hybrid pixels

- even larger area
- radhard sensors
- higher rates R/O

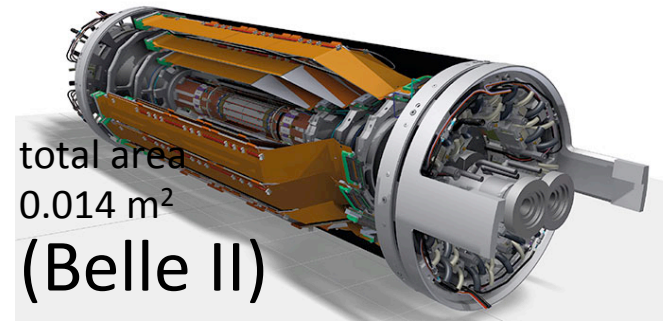
(Semi)-Monolithic Pixel Detectors

STAR / RHIC **MAPS**



total area
 0.16 m^2

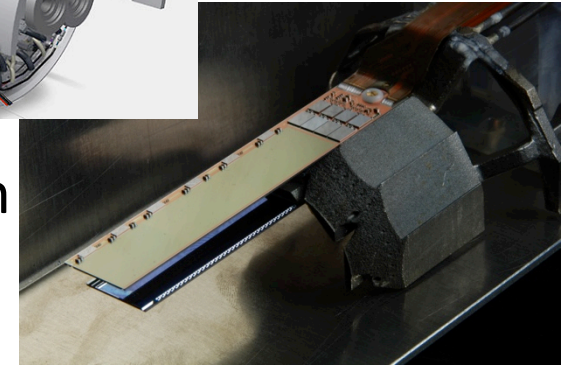
operated 2014-2015



total area
 0.014 m^2
(Belle II)

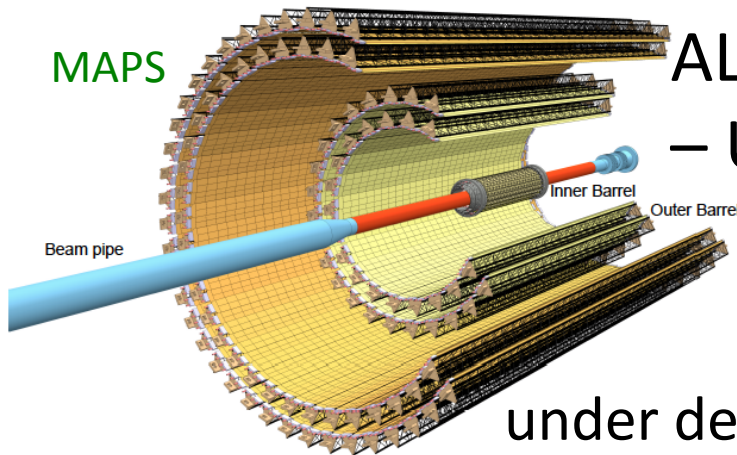
DEPFET pixels

in production
for 2017



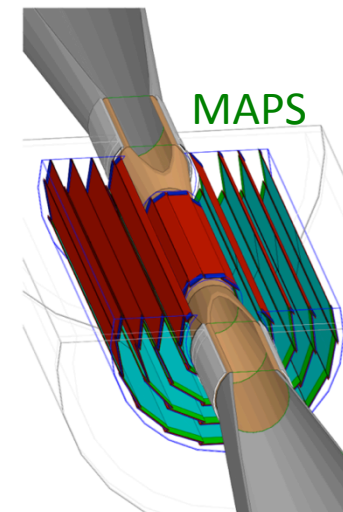
MAPS

ALICE
– Upgrade



total area
 $\sim 10 \text{ m}^2$

under development
target: 2018



MAPS

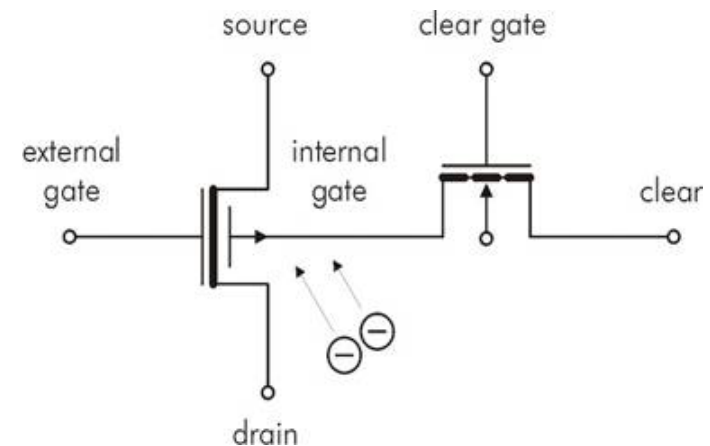
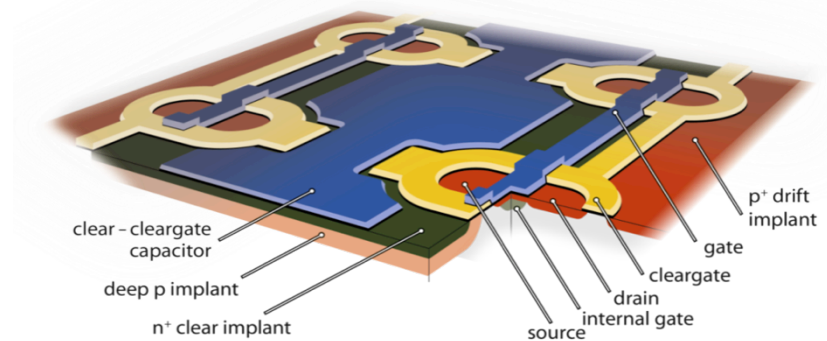
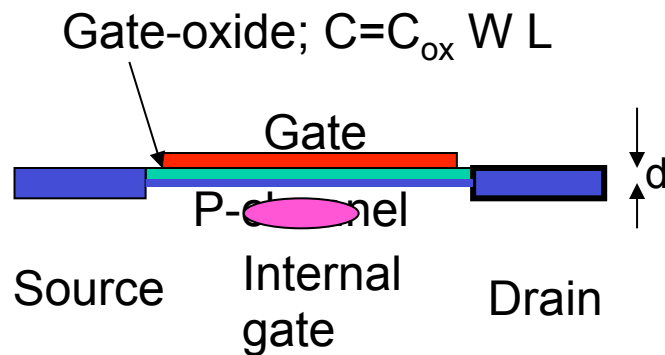
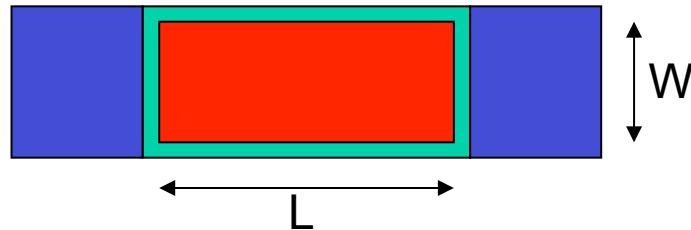
ILC

total area
 $? \text{ m}^2$

current
baseline



How does a DEPFET work?



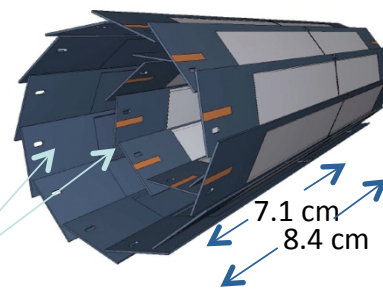
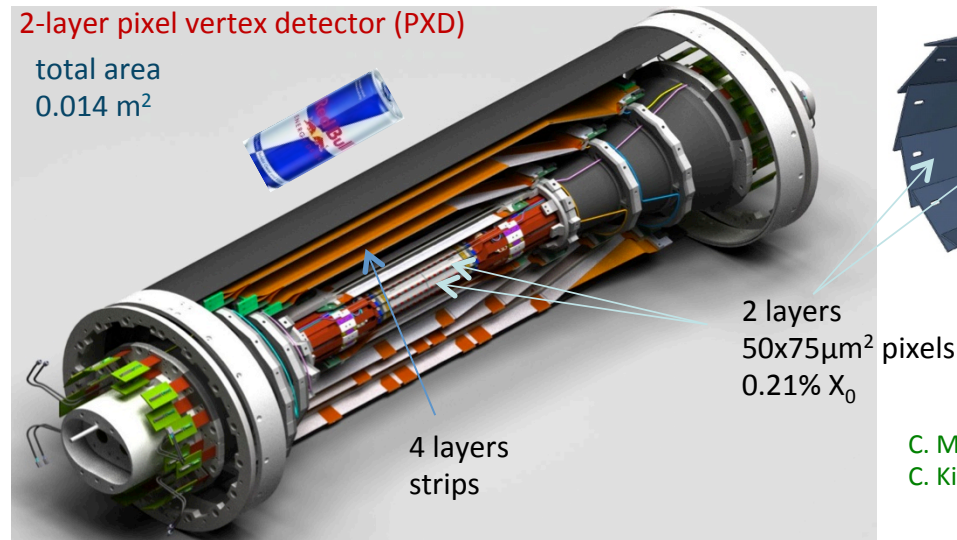
A charge q in the internal gate induces a (mirror) charge αq in the channel/external gate ($\alpha < 1$ due to stray capacitance) **changing the gate voltage**: $\Delta V = \alpha q / (C_{ox} W L)$ which in turn changes the transistor current I_d .



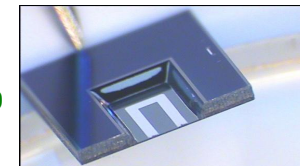
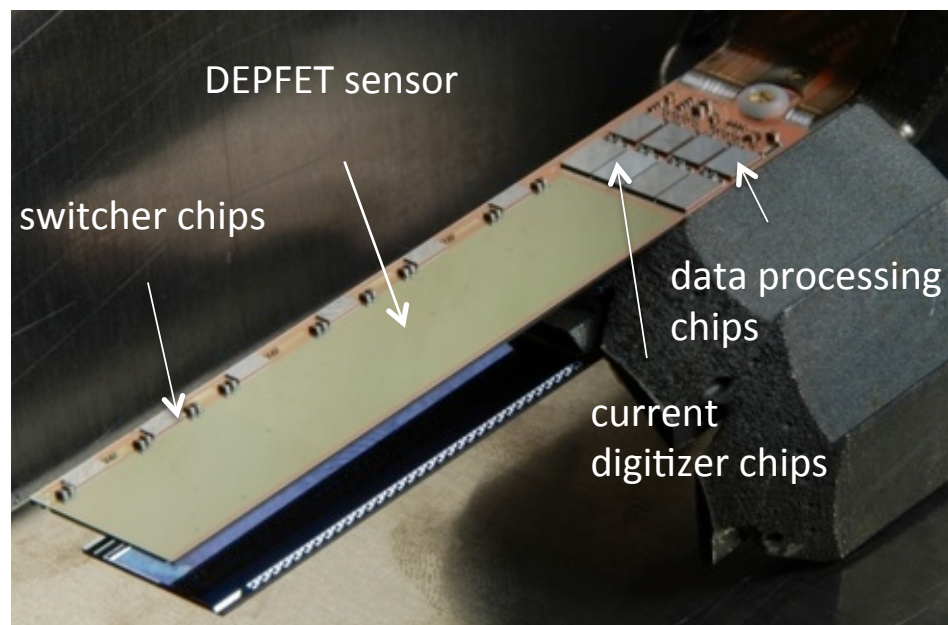
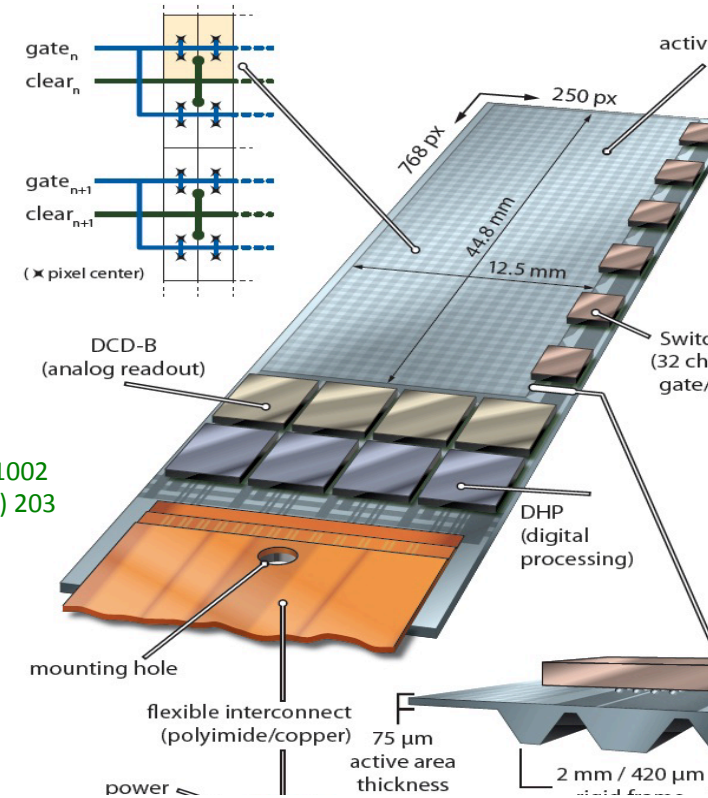
features:

- $g_q \sim 700 \text{ pA/e}^-$
- small intrinsic noise
- sensitive off-state, w/o power used

BELLE II DEPFET Pixel Detector



C. Marinas et al., JINST 10 (2015) 11, C11002
C. Kiesling et al., PoS EPS-HEP2011 (2011) 203

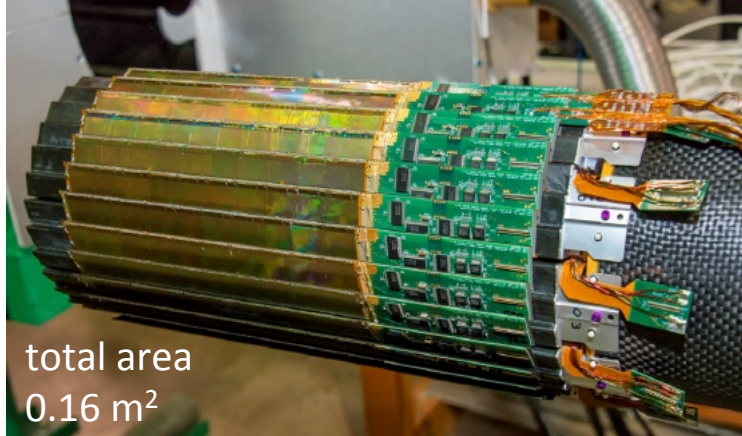


L. Andricek,
IEEE Trans.Nucl.Sci. 51 (2004) 1117-1120

(Semi)-Monolithic Pixel Detectors

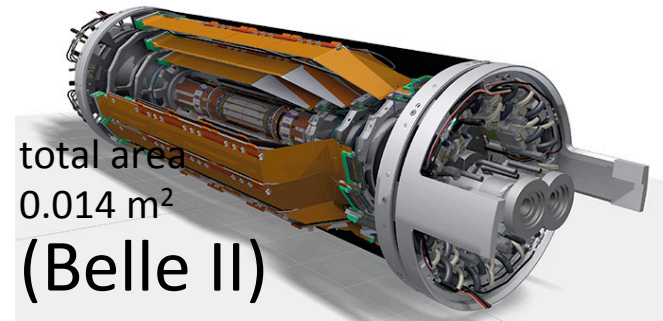
STAR / RHIC

MAPS



total area
 0.16 m^2

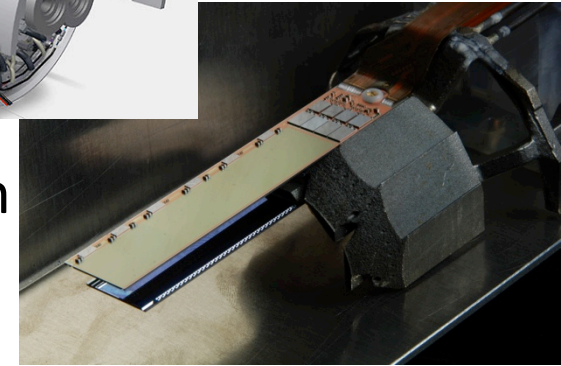
operated 2014-2015



total area
 0.014 m^2
(Belle II)

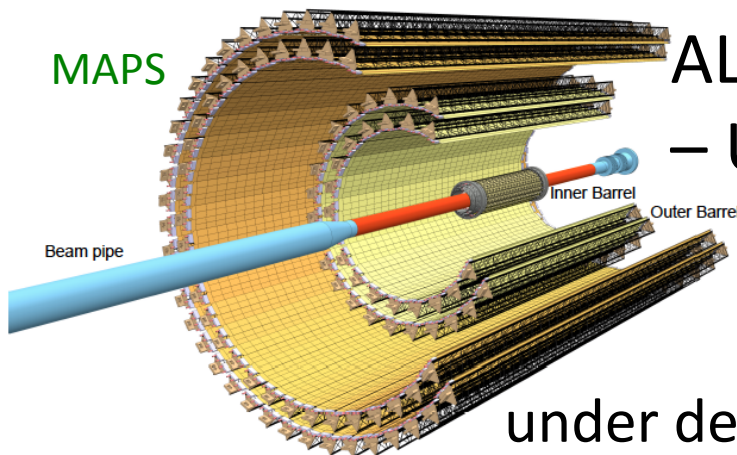
DEPFET pixels

in production
for 2017



MAPS

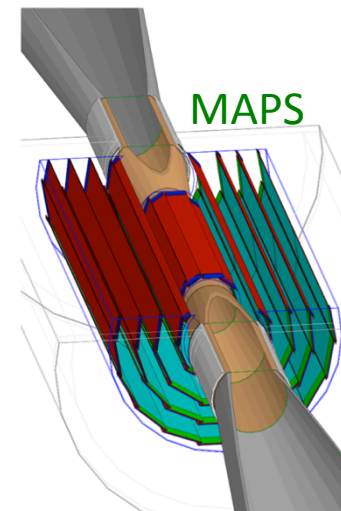
ALICE
– Upgrade



total area
 $\sim 10 \text{ m}^2$

under development
target: 2018

ILC

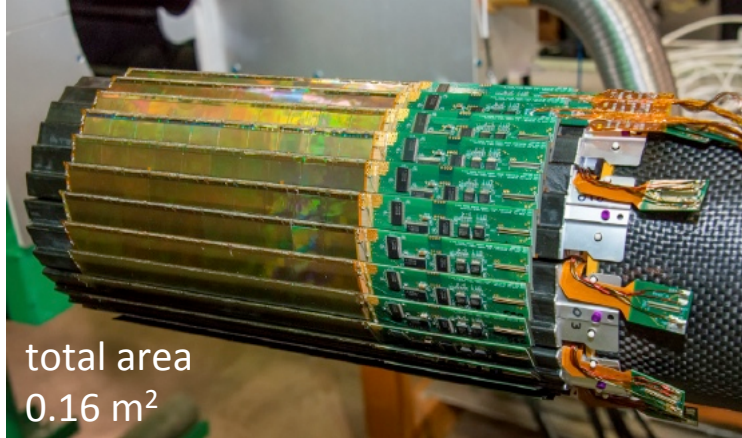


MAPS

total area
 $? \text{ m}^2$

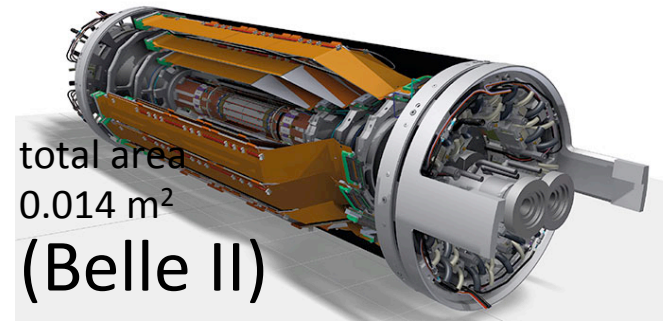
current
baseline

STAR / RHIC MAPS



total area
0.16 m²

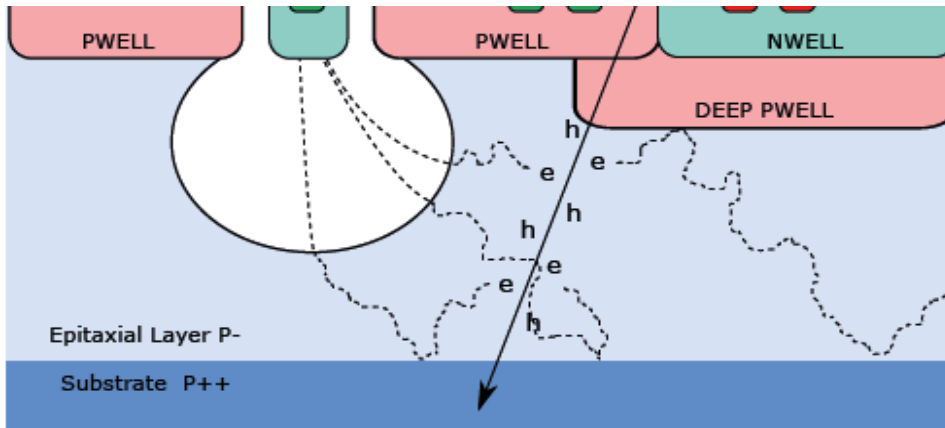
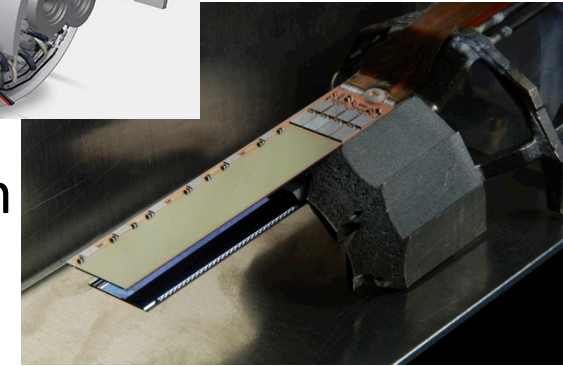
operated 2014-2015



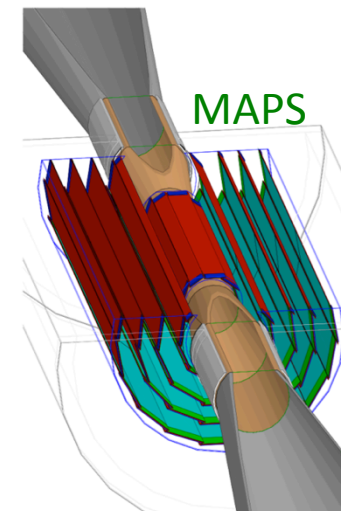
total area
0.014 m²
(Belle II)

DEPFET pixels

in production
for 2017



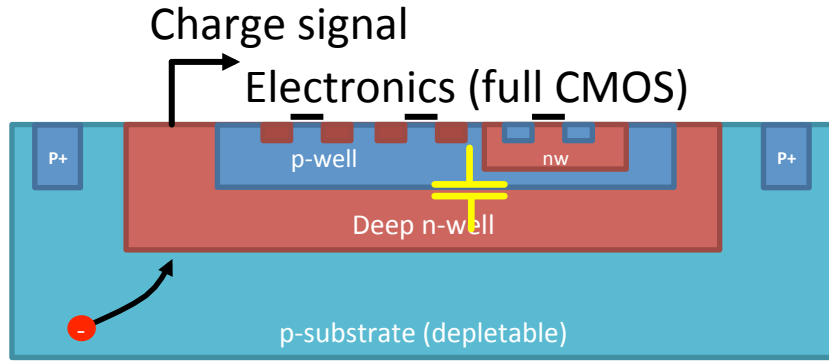
radiation tolerant to 1/1500 of HL-LHC-pp



ILC

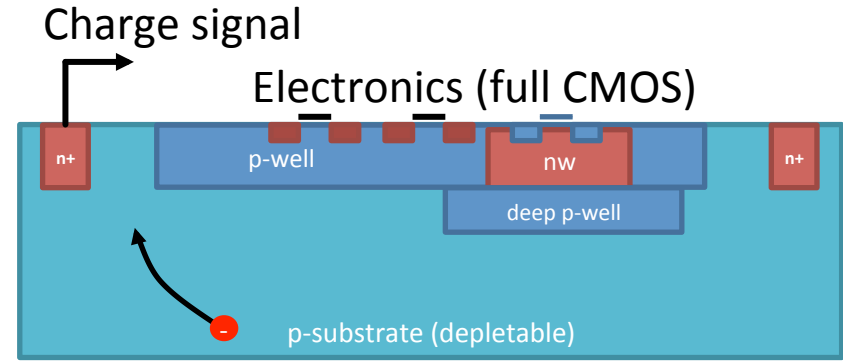
total area
? m²

current
baseline



Electronics **inside** charge collection well

- **large fill factor**
 - no low field regions
 - on average **short(er) drift** distances
 - less trapping -> **radiation hard**
- **Larger (100 fF) sensor capacitance**
- **additional well-well capacitance** (~100 fF)
 - noise & speed/power penalties
 - x-talk easier (from digital to sensor)



Electronics **outside** charge collection well

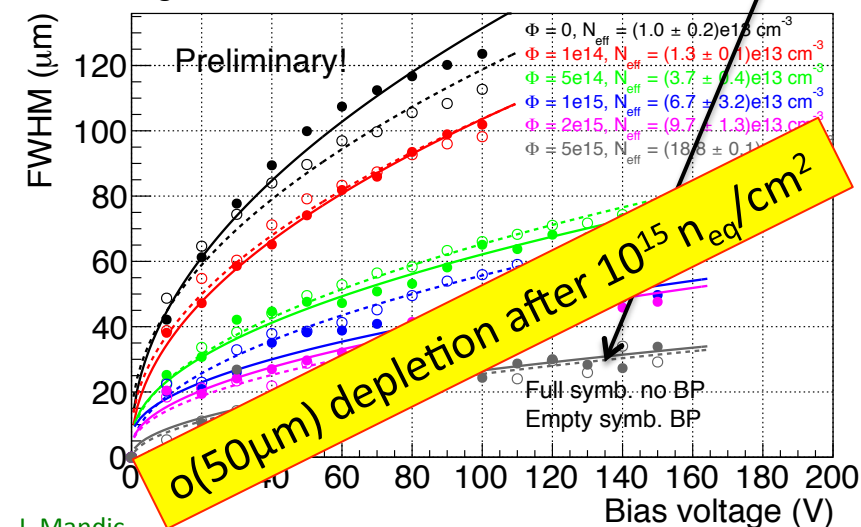
- **small fill factor**
 - > **very small sensor capacitance (~5 fF)**
 - noise low, speed high, power low
- on average longer drift distances and low field regions
 - **not radhard ? or ??**

Goal-1 ... $S/N \approx 20$, i.e. $N \lesssim 200e^- \Rightarrow S = 4000e^- (\triangleq 50\mu m)$

• radiation hardness

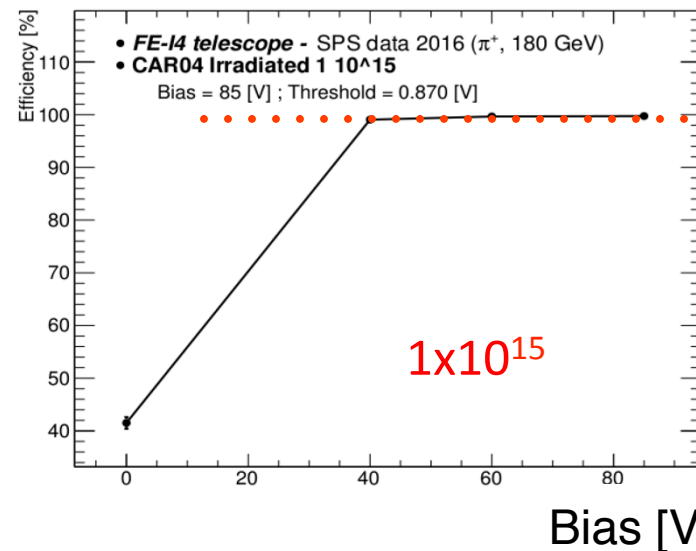
LFoundry

edge-TCT measurements



I. Mandic

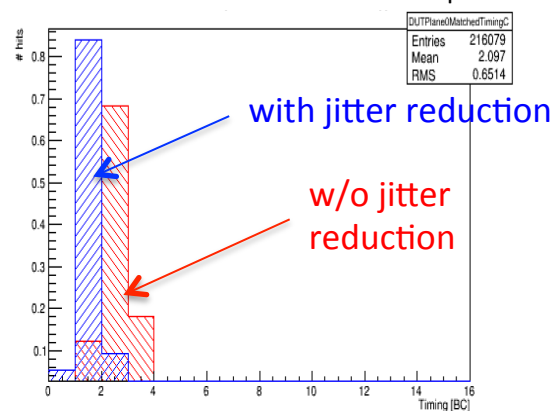
• efficiency



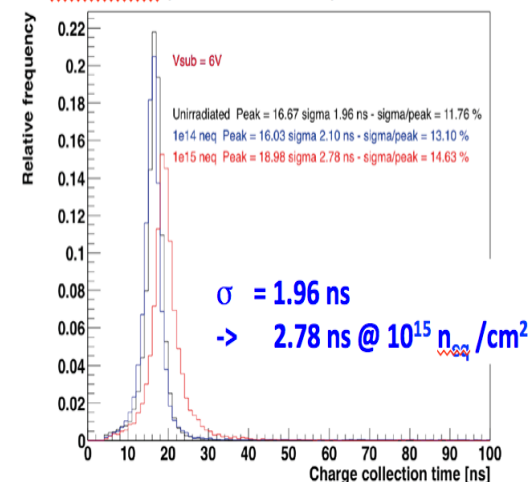
... 99.7%
(time integrated)

• timing

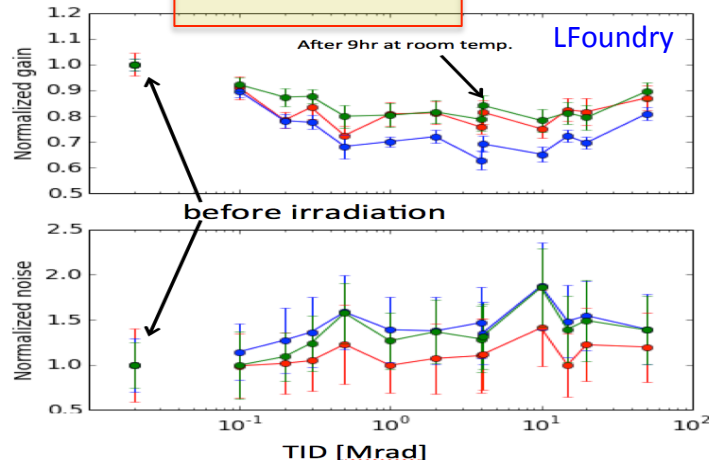
AMS180 after $1 \times 10^{15} n_{eq}/cm^2$



TowerJazz (small fill factor)



TID 100 Mrad



gain

noise

N. Werme

4D with LGADs?

Low Gain Avalanche Detectors

30 ps timing precision?

New: How to obtain fast timing with Si detectors?

❑ 10 - 30 ps with (structured) Si detectors ??

❑ => exploit “in-silicon” charge amplification

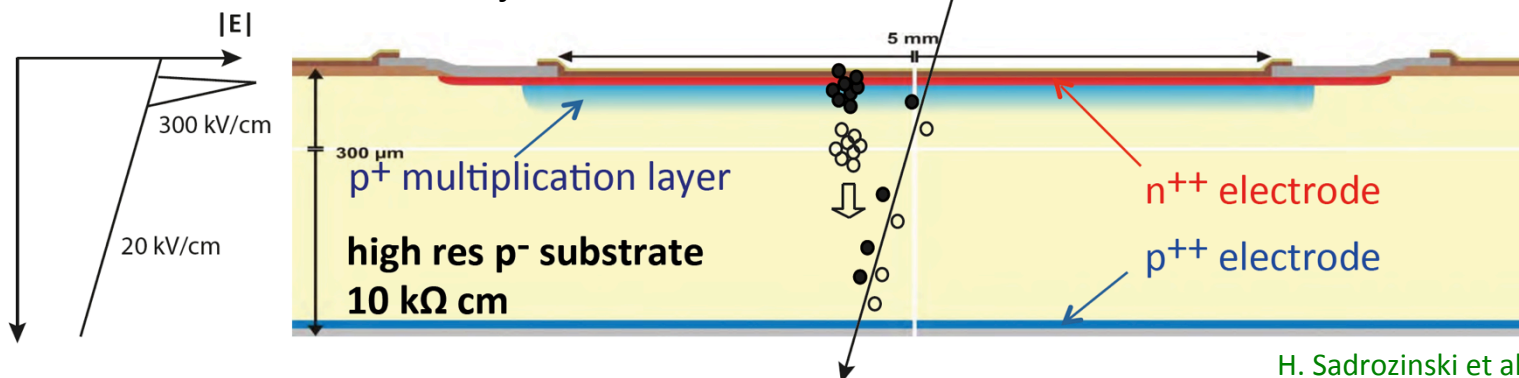
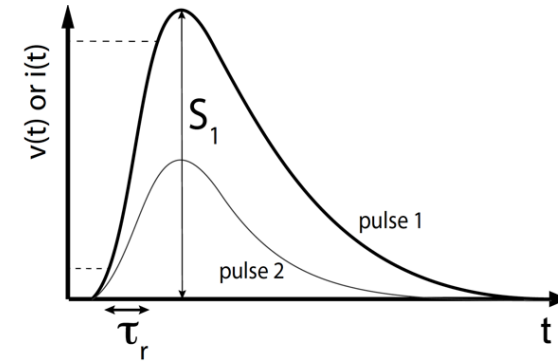
▪ in “Geiger Mode” fashion (like in gas **RPCs**) → σ_t governed by avalanche fluctuations

OR in “linear mode” fashion (lower E-fields, lower shot noise, no dark counts)

-> Low Gain Avalanche Detectors

$$\sigma_t^2 = \underbrace{\left(\frac{V_{th}}{dV/dt} \right)_{rms}^2}_{\text{signal time walk}} + \underbrace{\left(\frac{\text{Noise}}{dV/dt} \right)^2}_{\text{noise time jitter}} + \underbrace{\left(\frac{TDC_{bin}}{\sqrt{12}} \right)^2}_{\text{TDC binning can be made negligible}}$$

“slew rate”



$$i_S = q \vec{E}_w \cdot \vec{v}$$

H. Sadrozinski et al., NIM A730 (2013) 226-231
N. Cartiglia et al., JINST 9 (2014) C02001
A. Seiden et al, Vertex2015, Proceedings

❑ **Ultimate Goal:** simultaneous space ($\sim 10\mu\text{m}$) and time resolution (< 50 ps)

❑ Options for **ATLAS** (HighGranularityTimingDetector; Forward) -> pile-up killer and **CMS-TOTEM** (in Roman Pots)

LGAD – starting with PAD detectors

□ high voltage (800 - 1000 V)

- high field $\rightarrow$ fast e^-

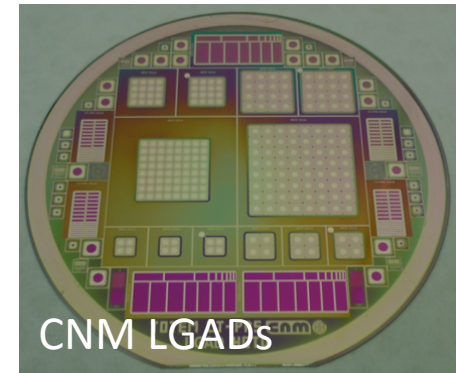
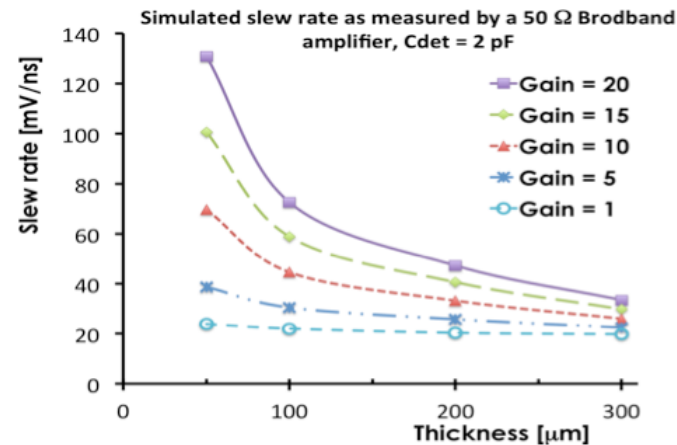
□ thin (50 μm)

- higher field for given voltage
- steeper signal
- rad harder
- smaller Landau spread

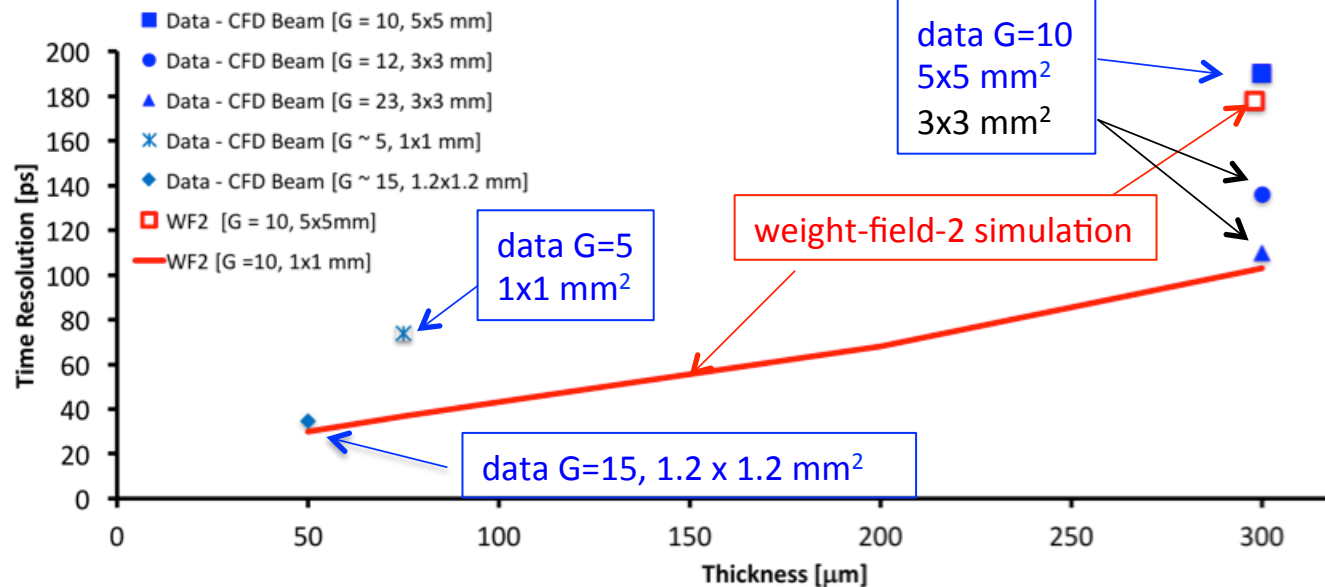
□ gain ~ 10

- lower E-fields
- lower shot noise,
- no/few dark counts

still pad detectors



G. Pellegrini et. al, NIM A 765 (2014) 12–16.



Conclusions

- ❑ Tracking Detectors (gas-filled, semiconductors, fibres) are facing highest challenges with HL-LHC upgrades and also generally.
- ❑ This will advance the physics potential at the (almost newly built) HL-LHC experiments.
- ❑ As usual almost certainly spin-offs (bio-medical) will emerge.
- ❑ “Detector Physics” has become a field of its own.

